

Figure 1 (Prior Art)

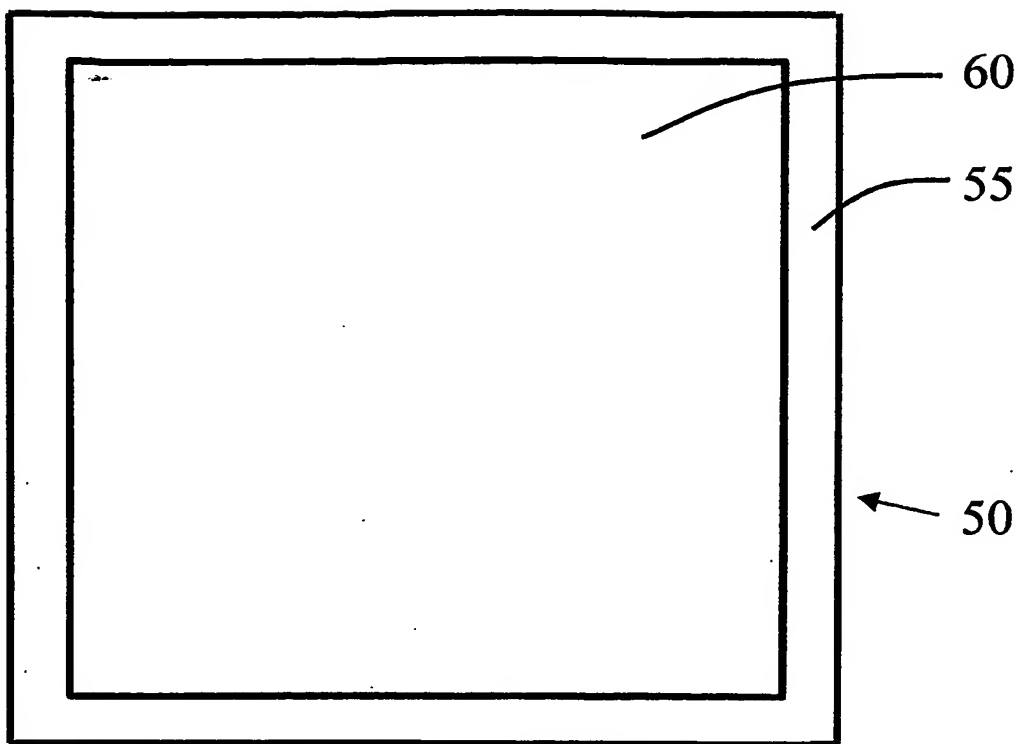


Figure 3

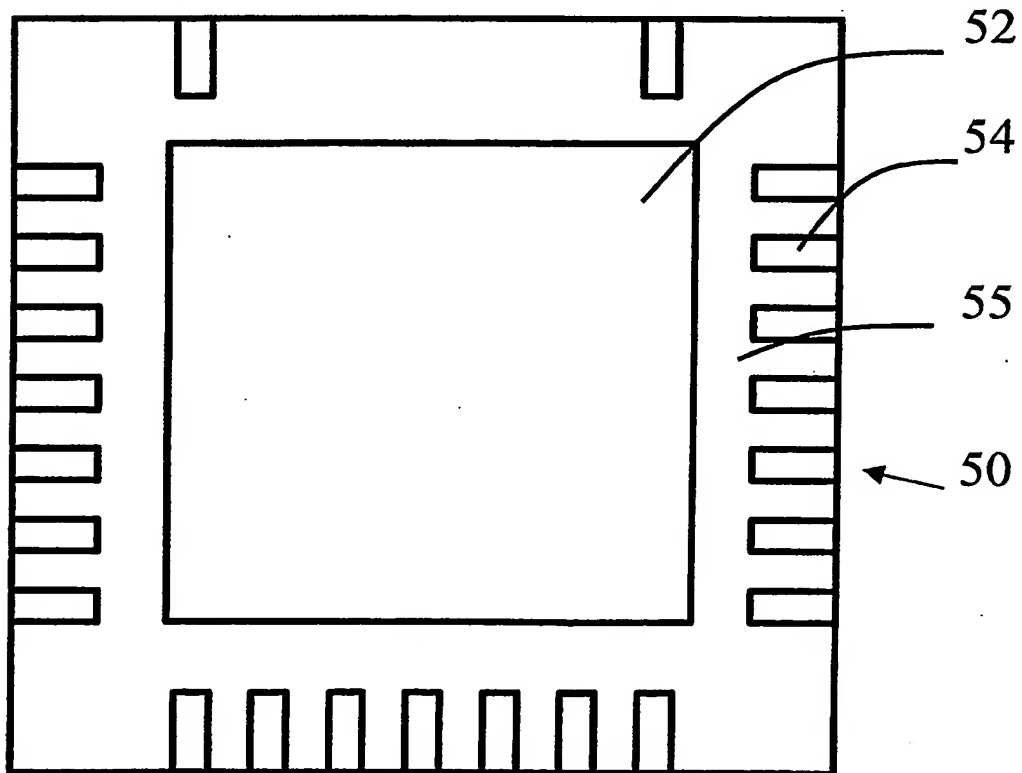


Figure 4

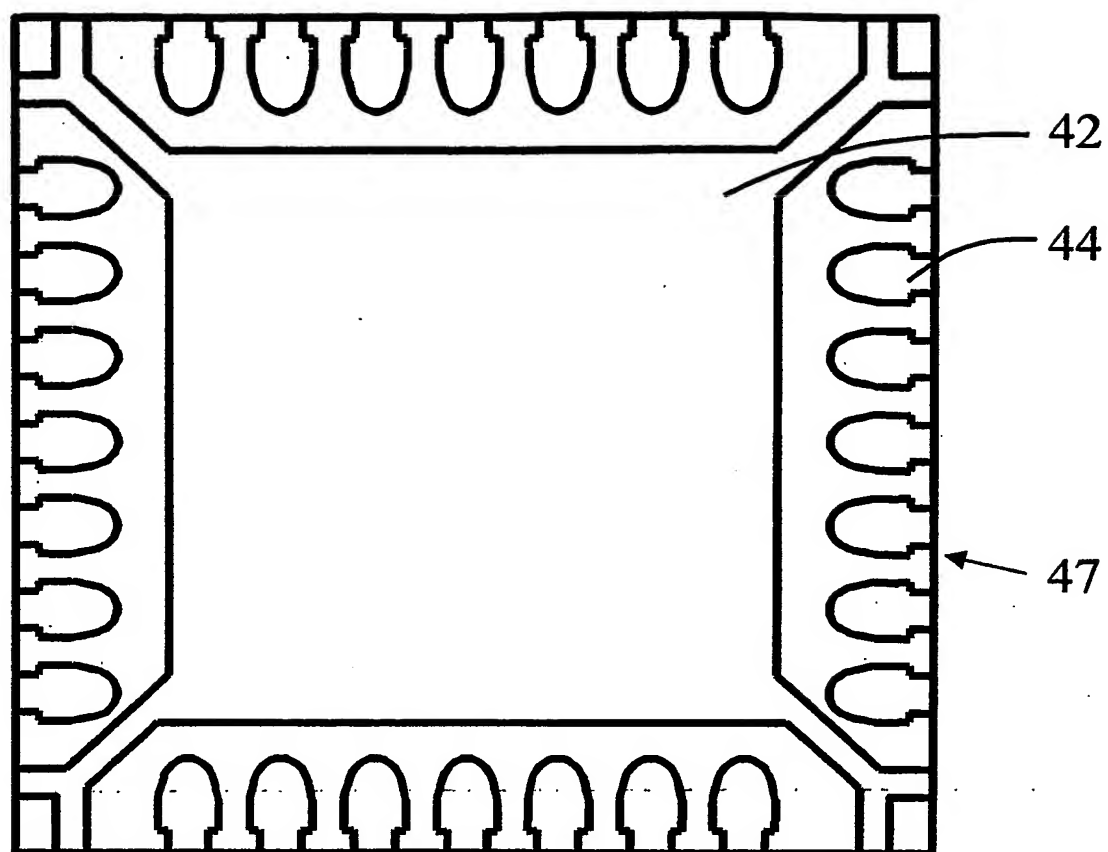


Figure 5

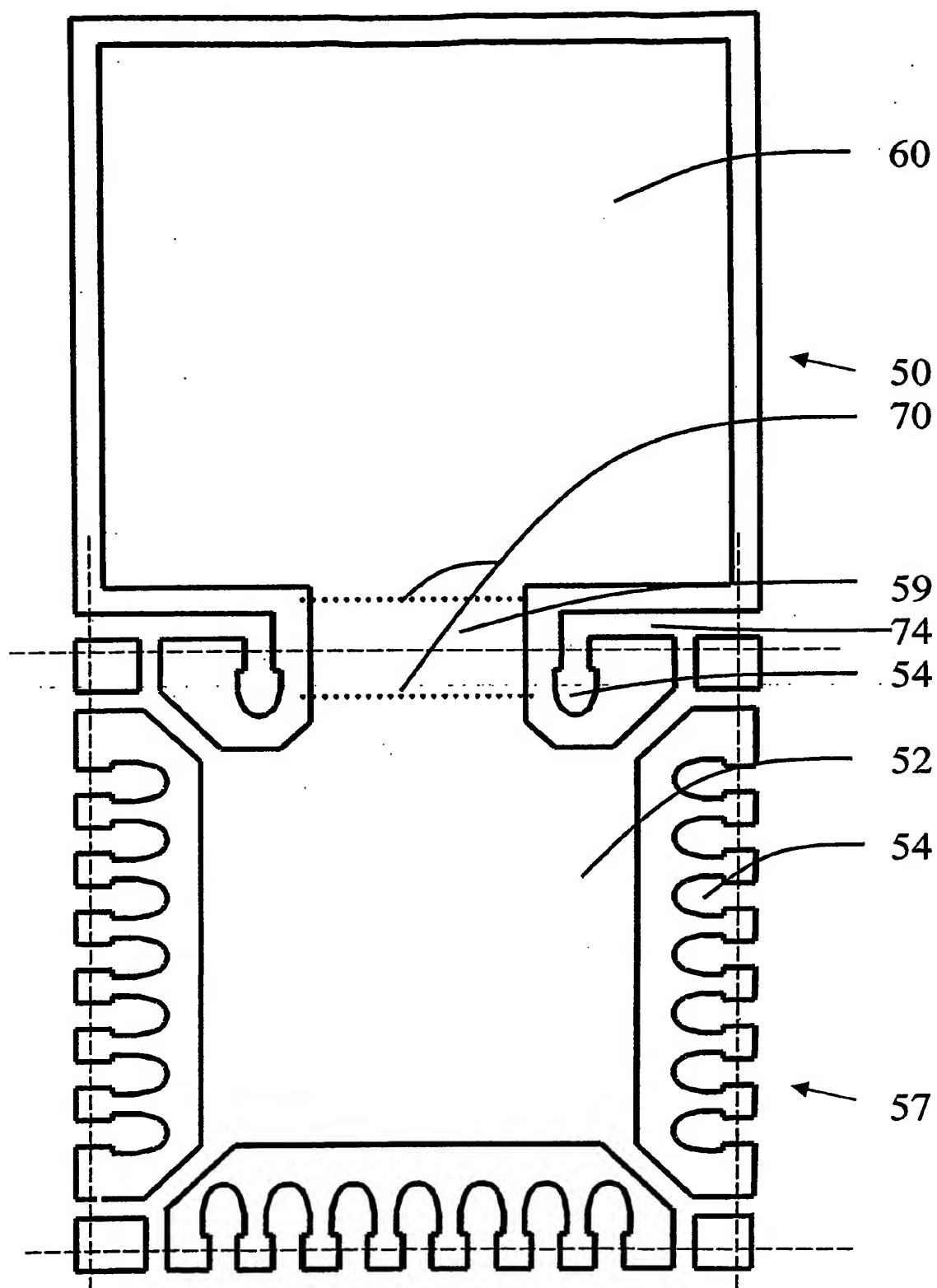


Figure 6

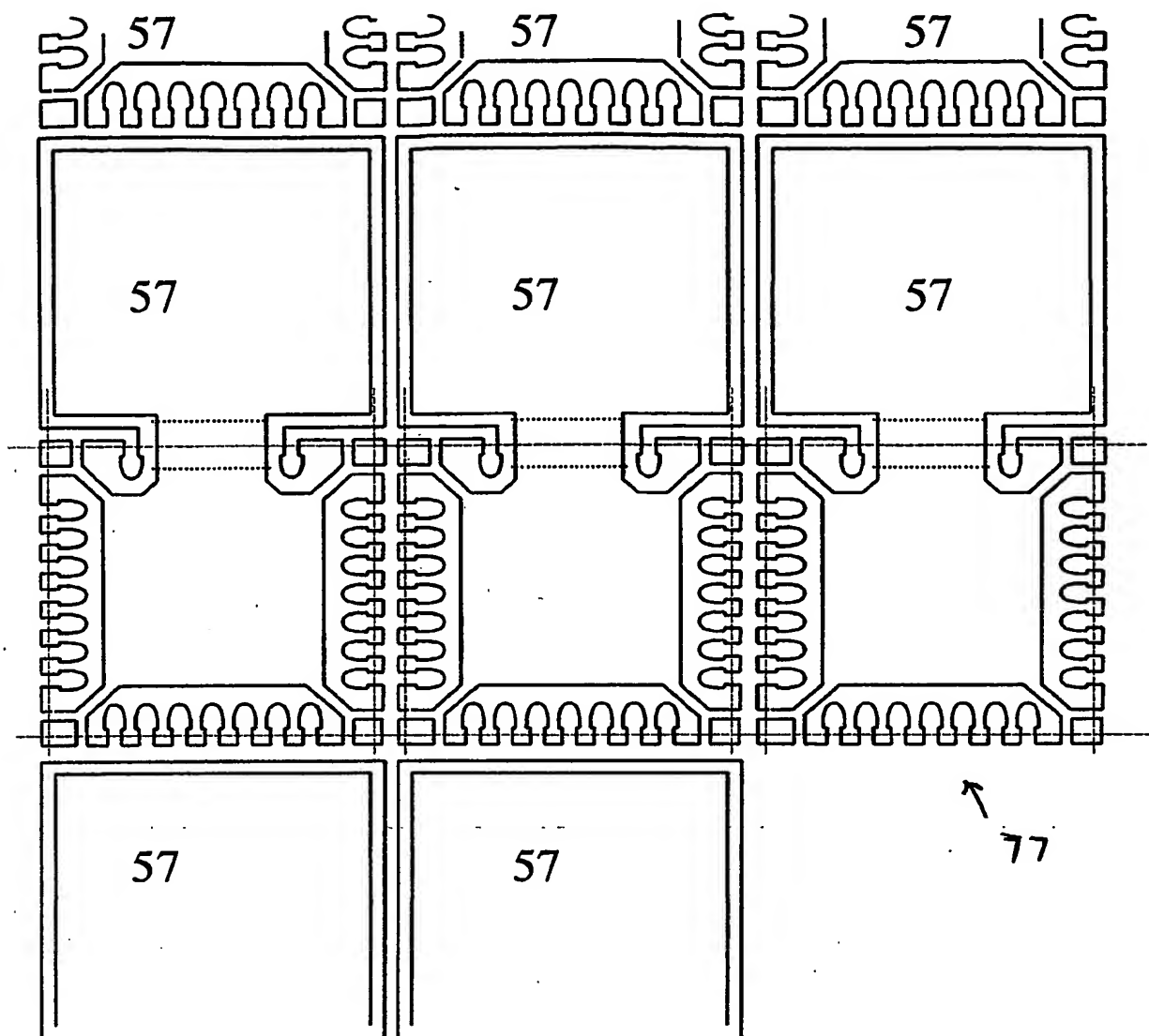


Figure 7

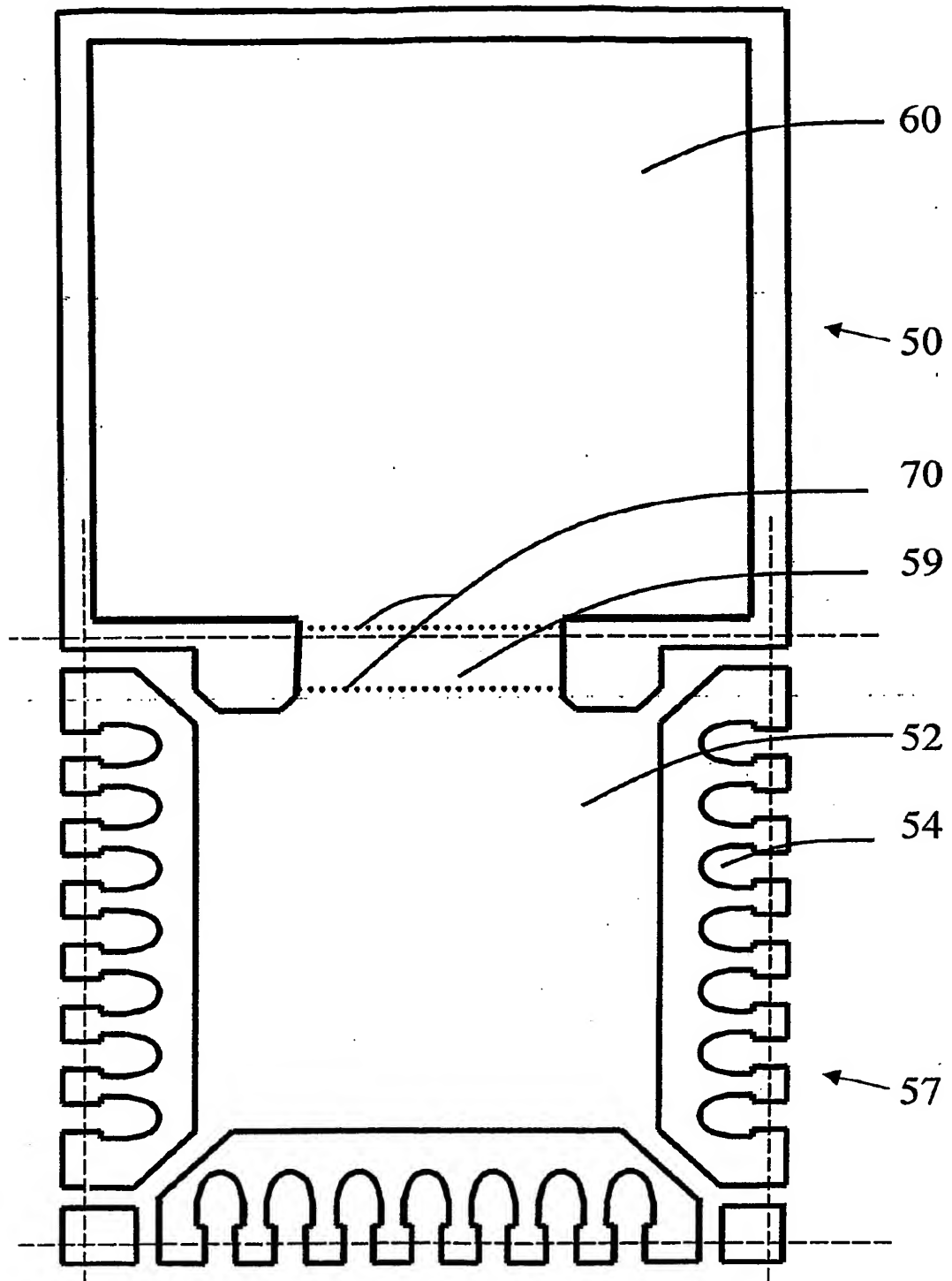


Figure 8

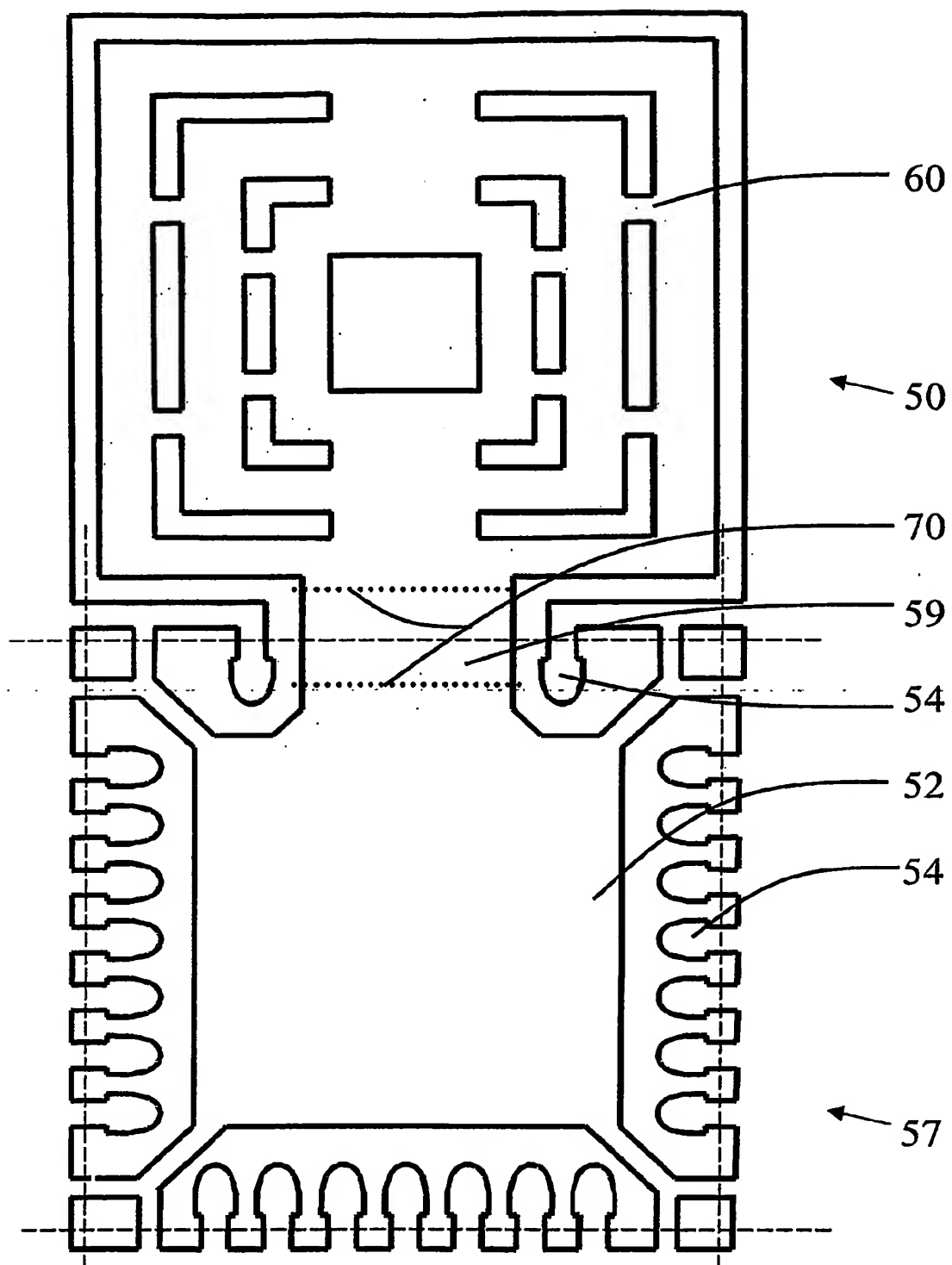


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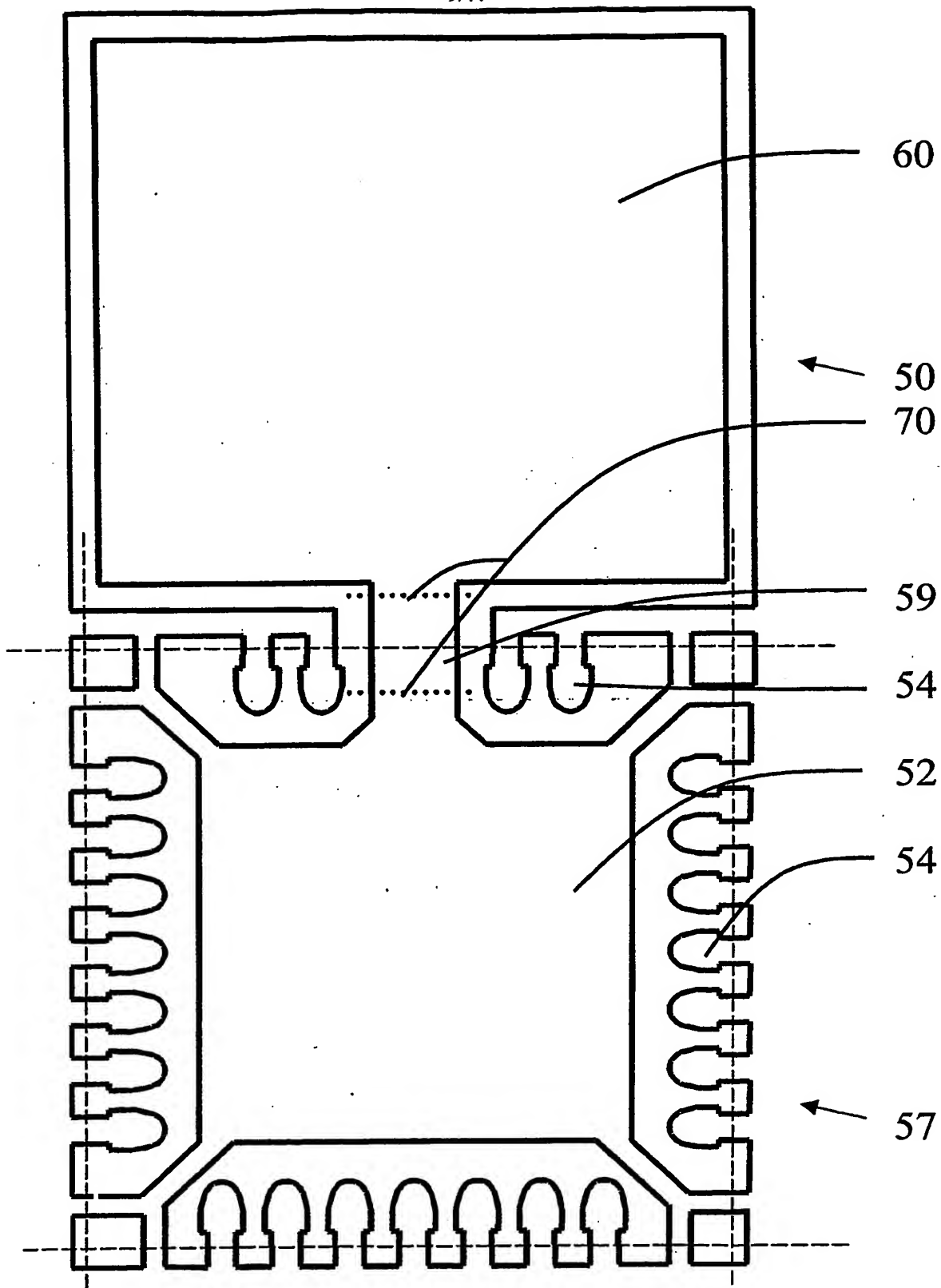


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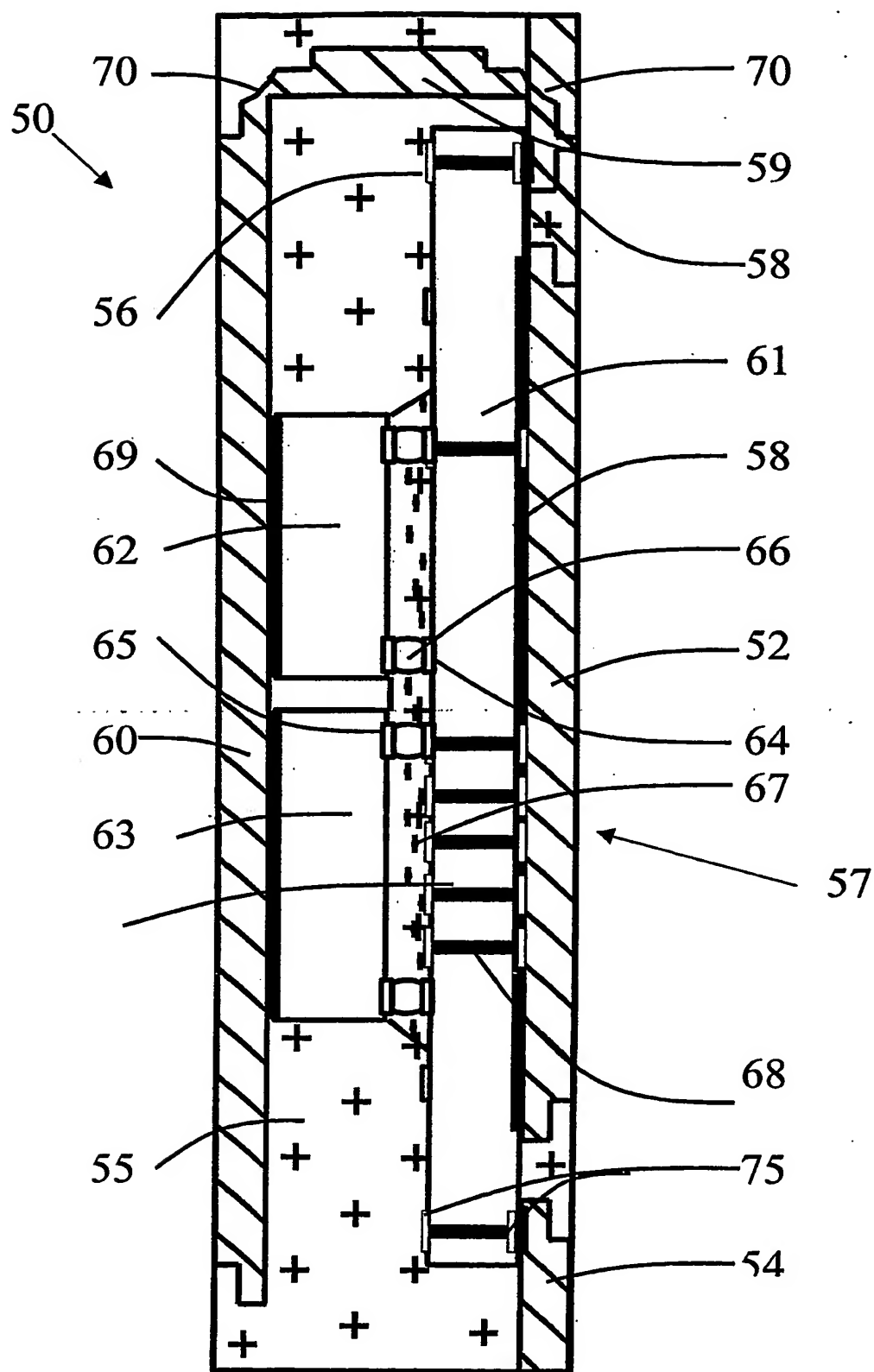


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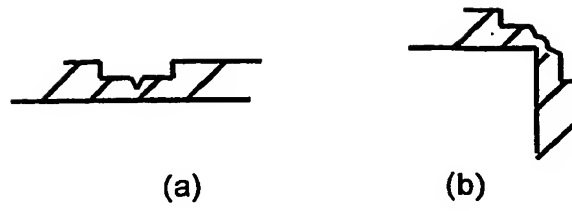


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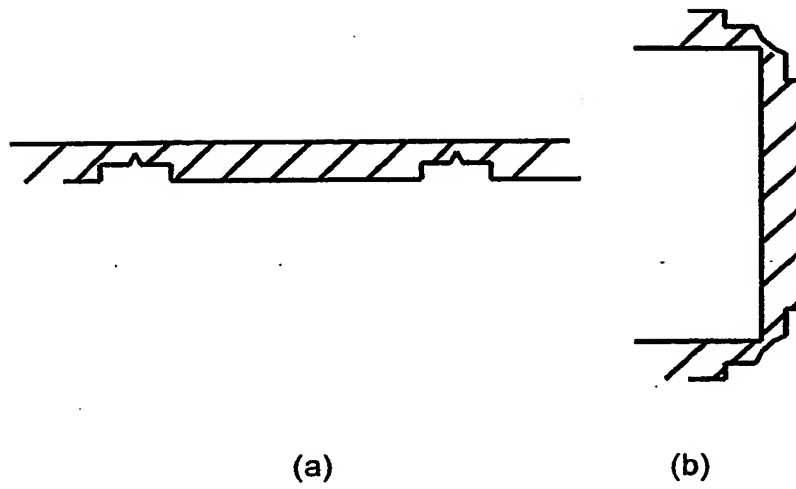


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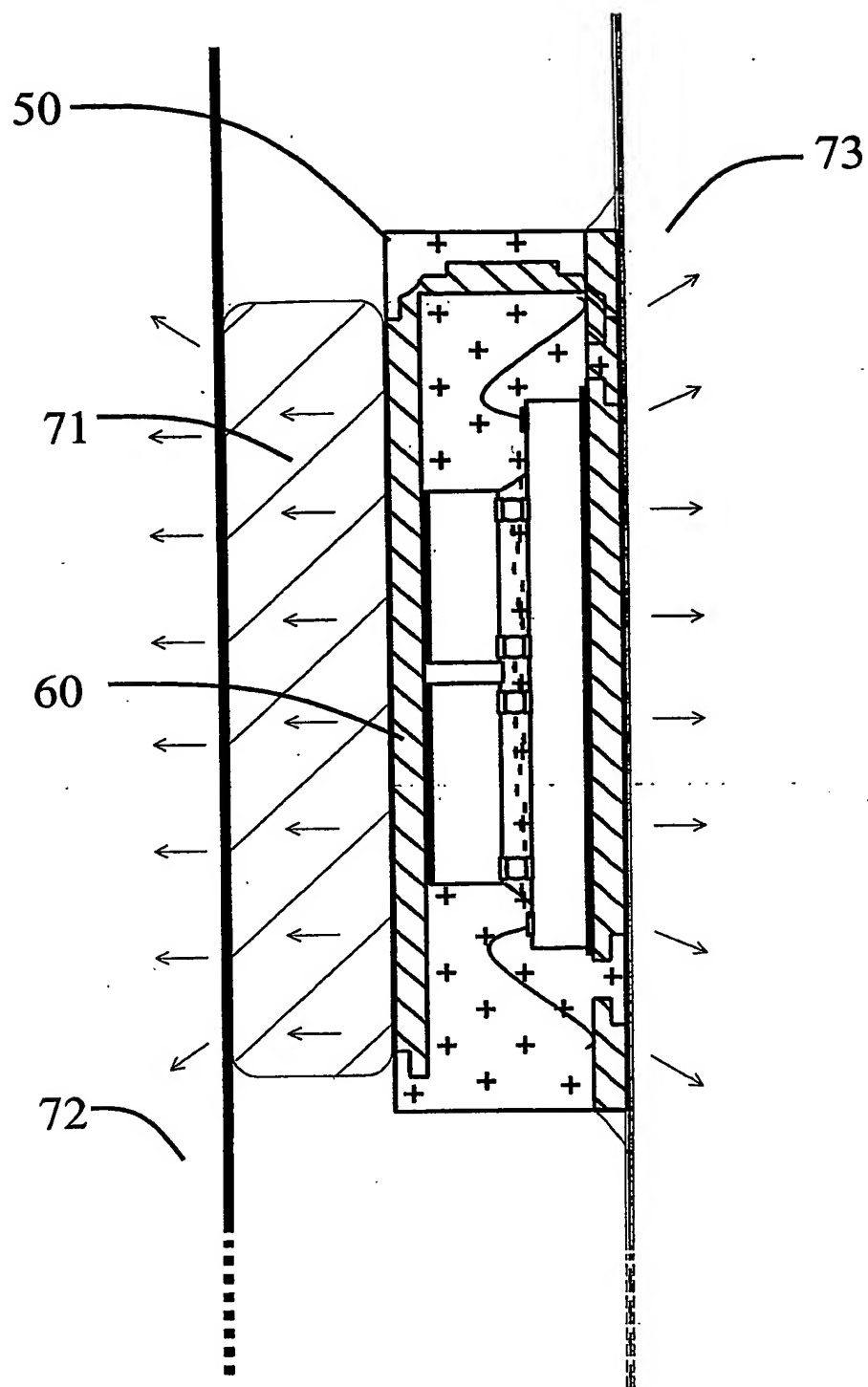


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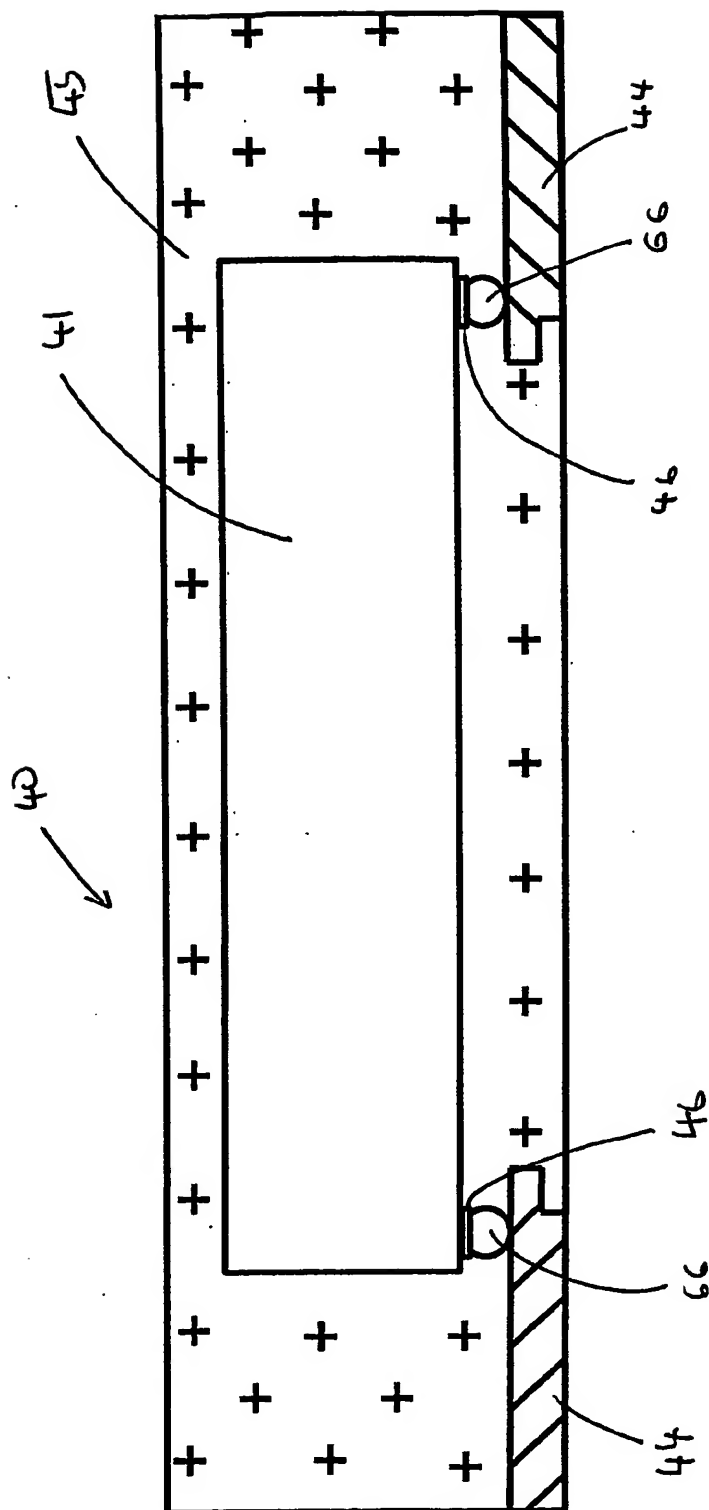


Figure 16 Prior Art

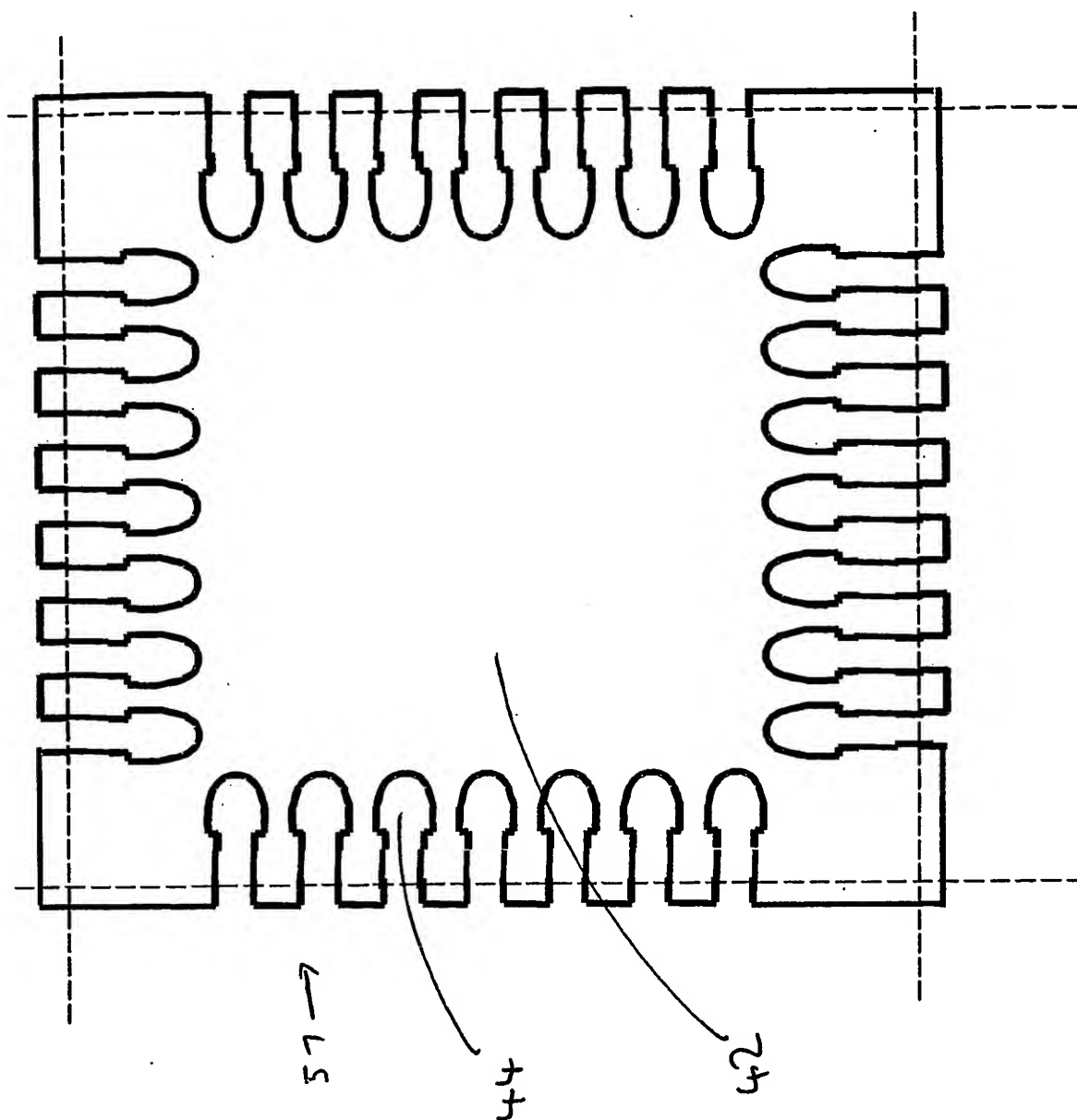


Figure 17 Prior Art

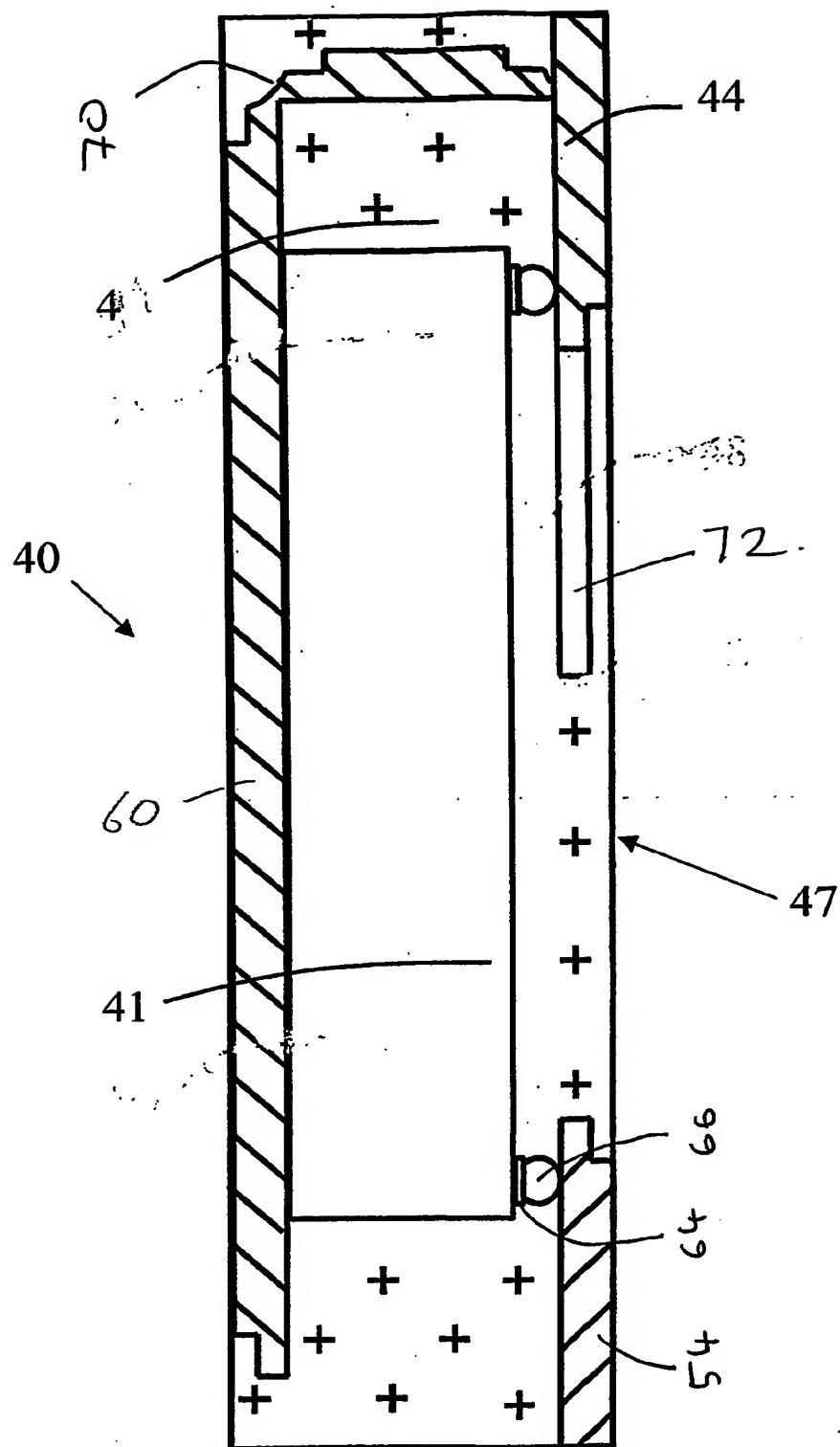


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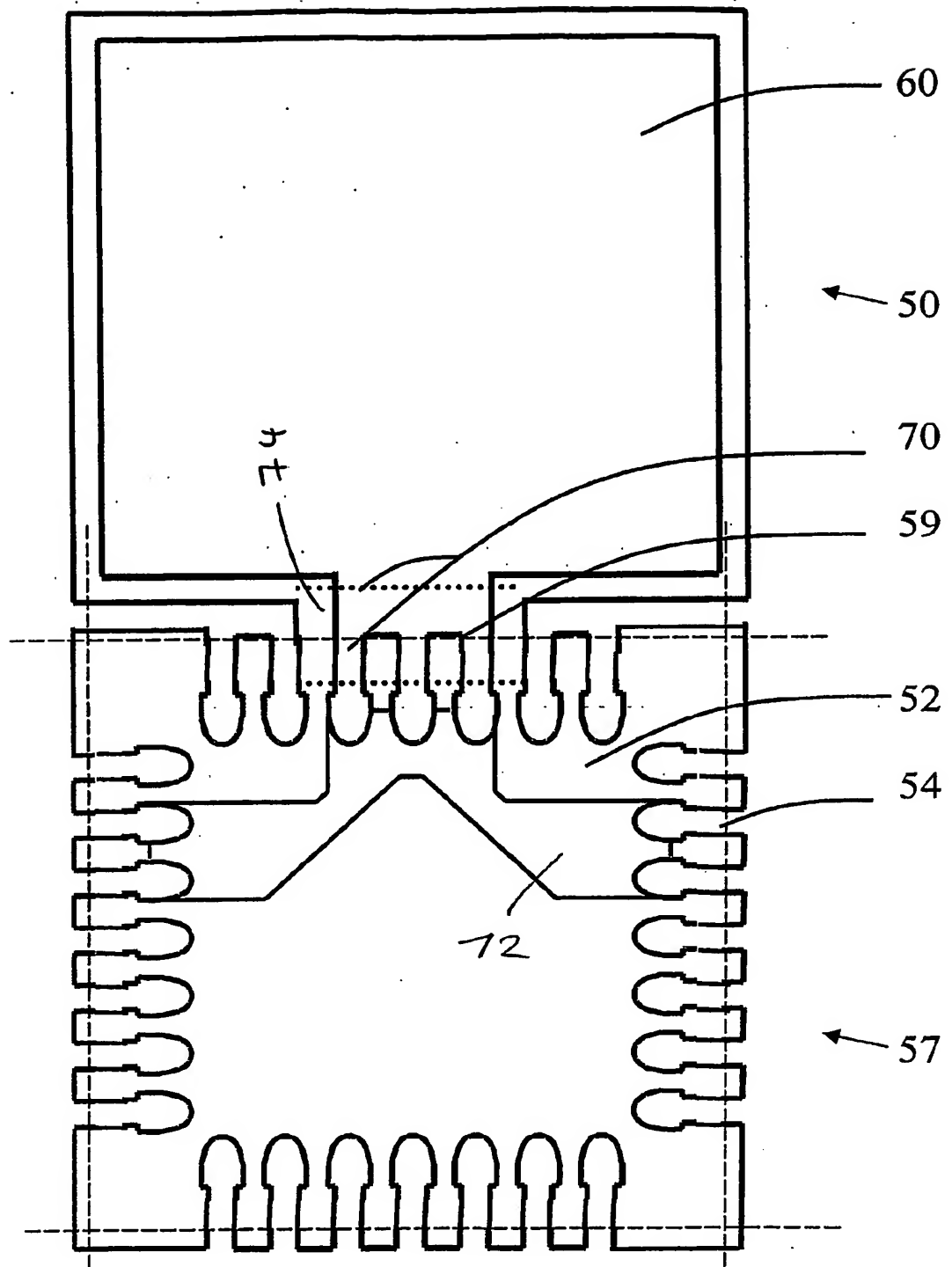


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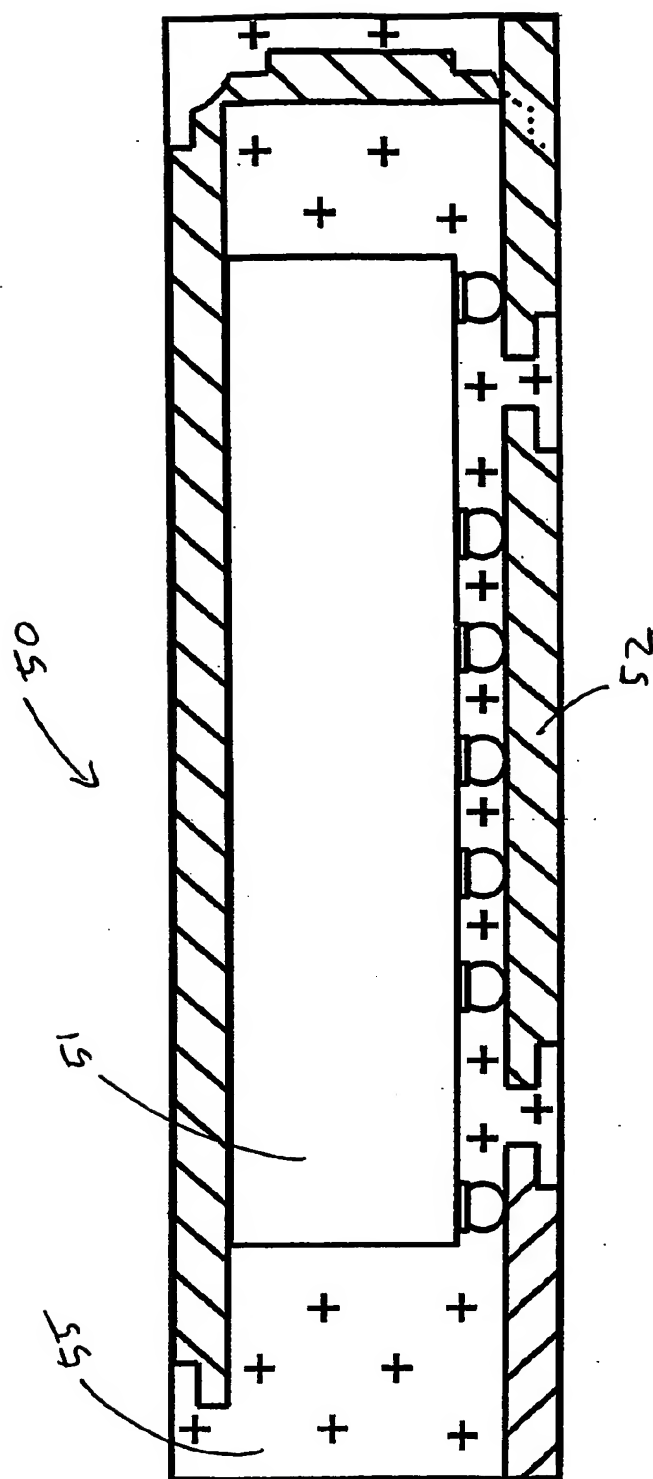


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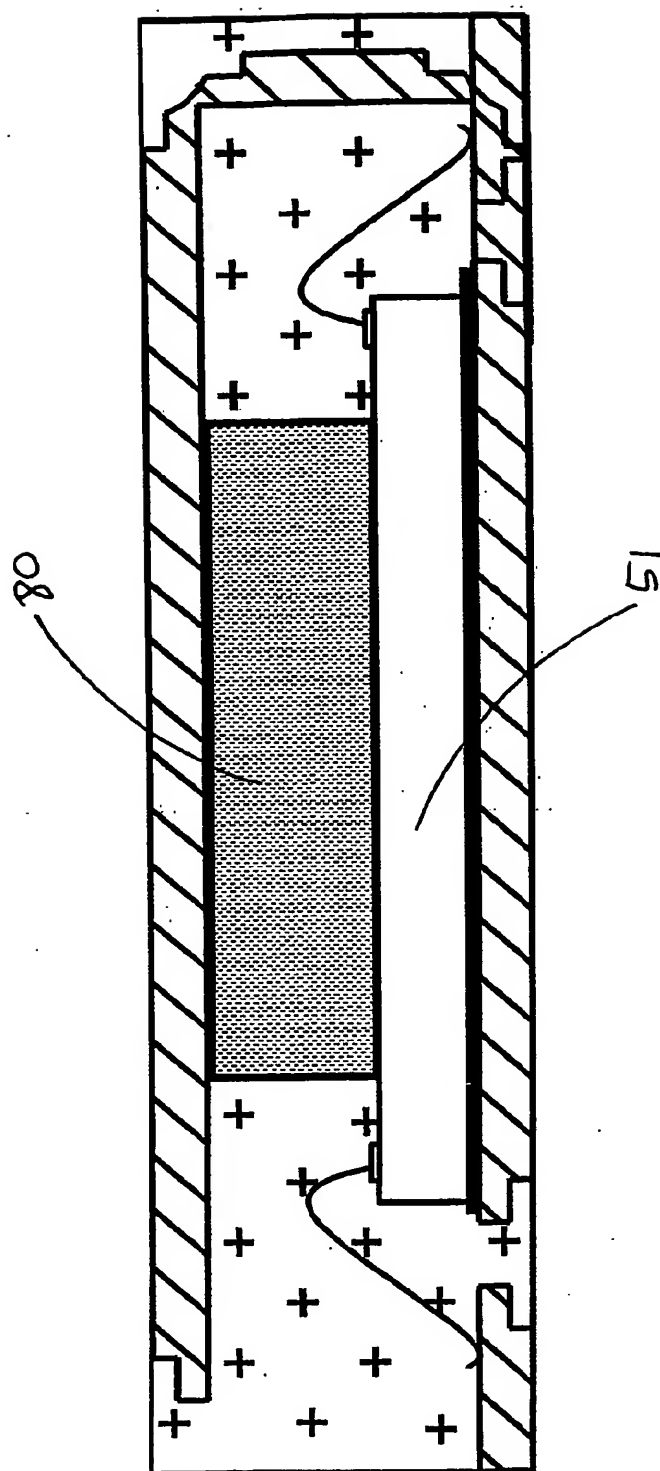


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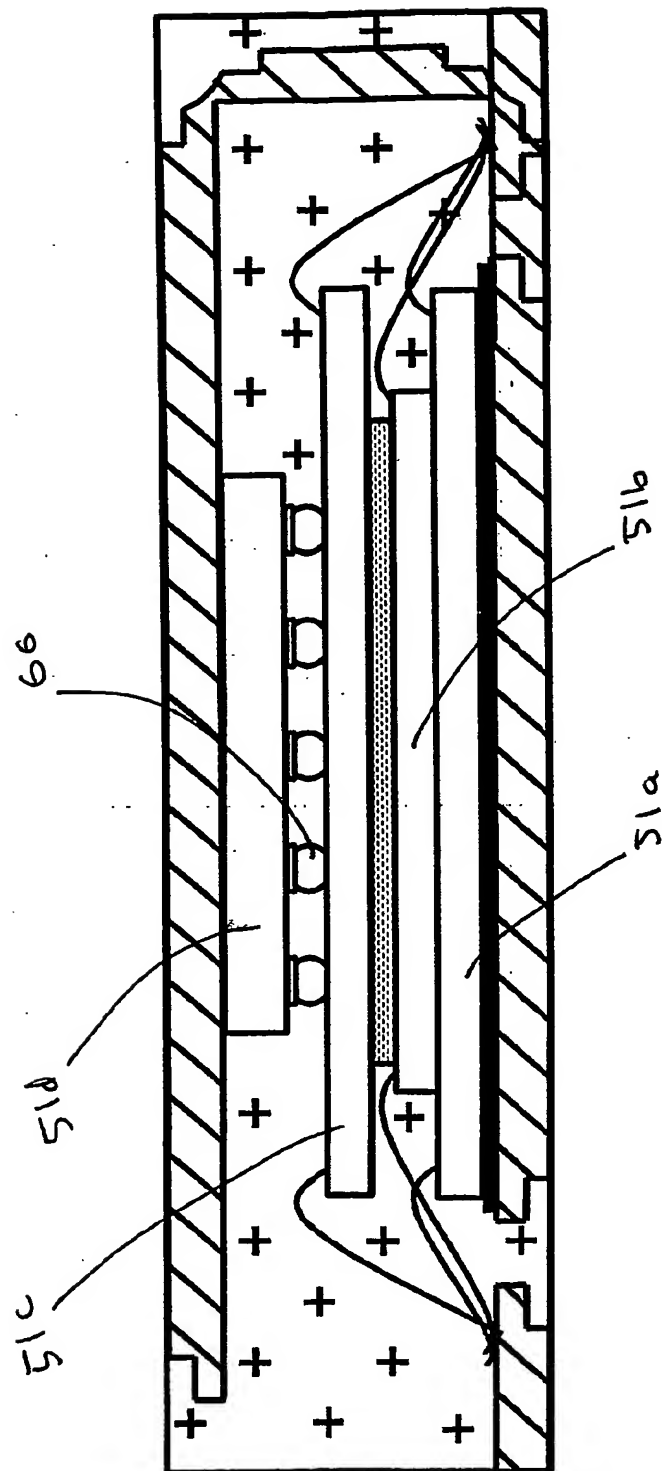


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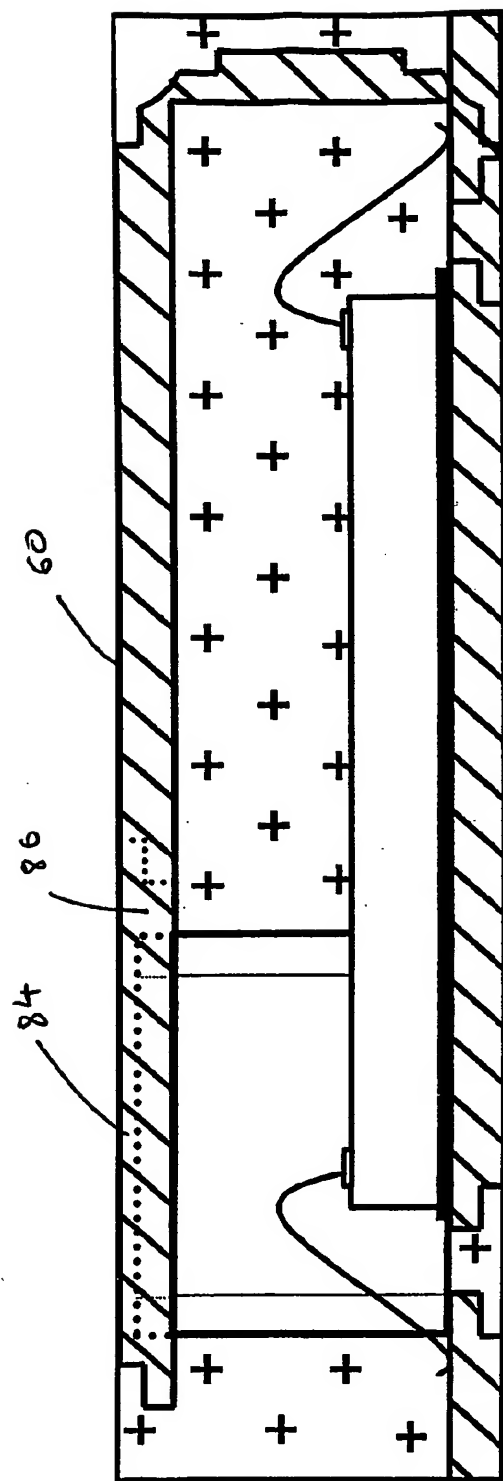


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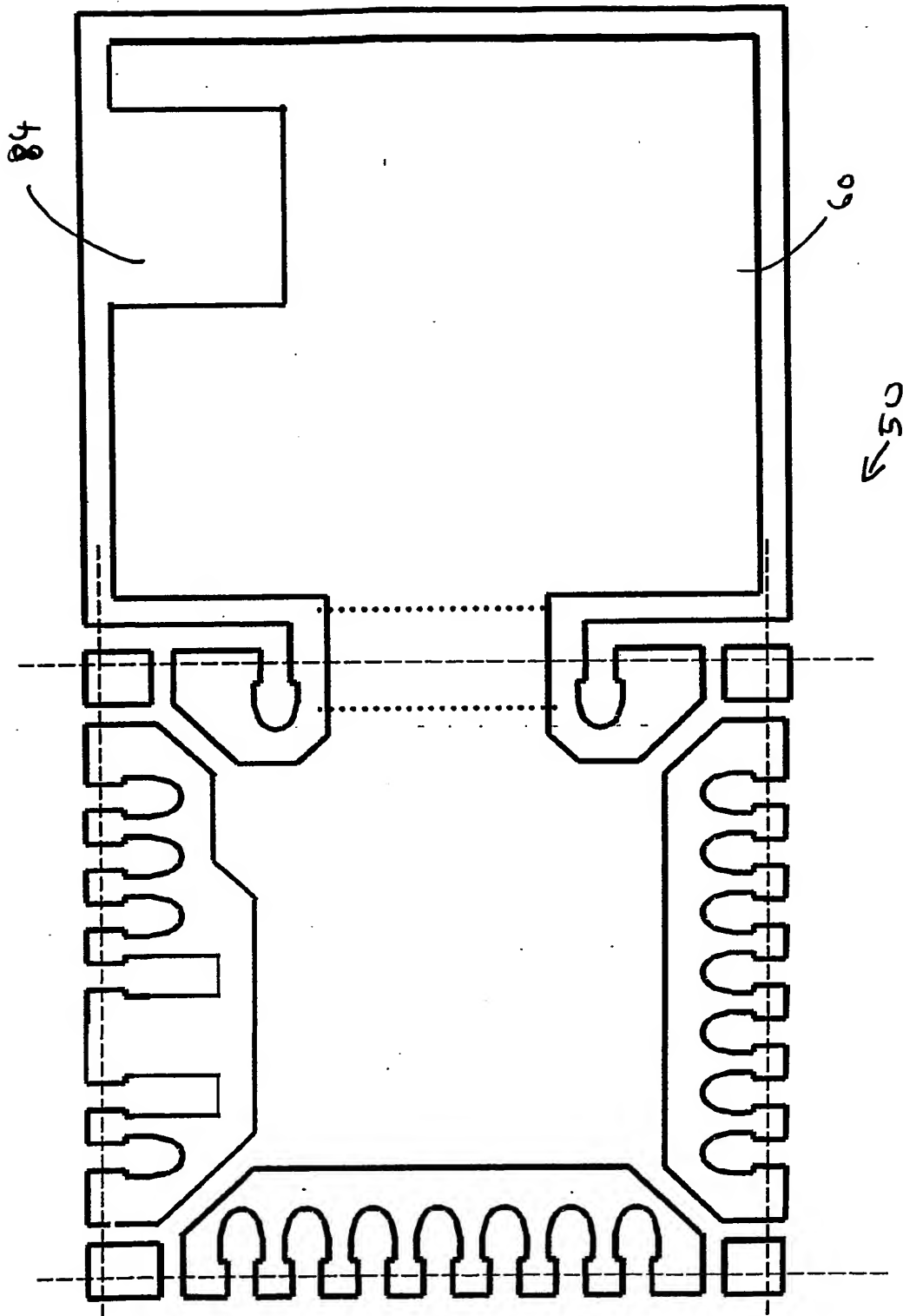


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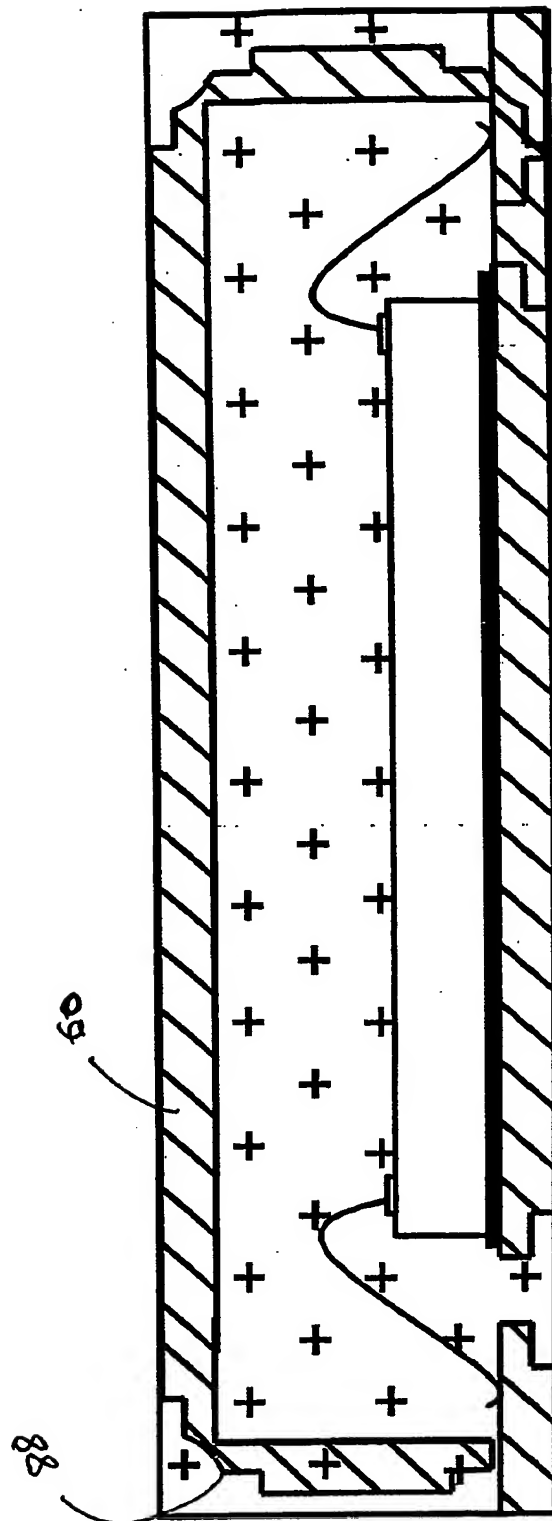


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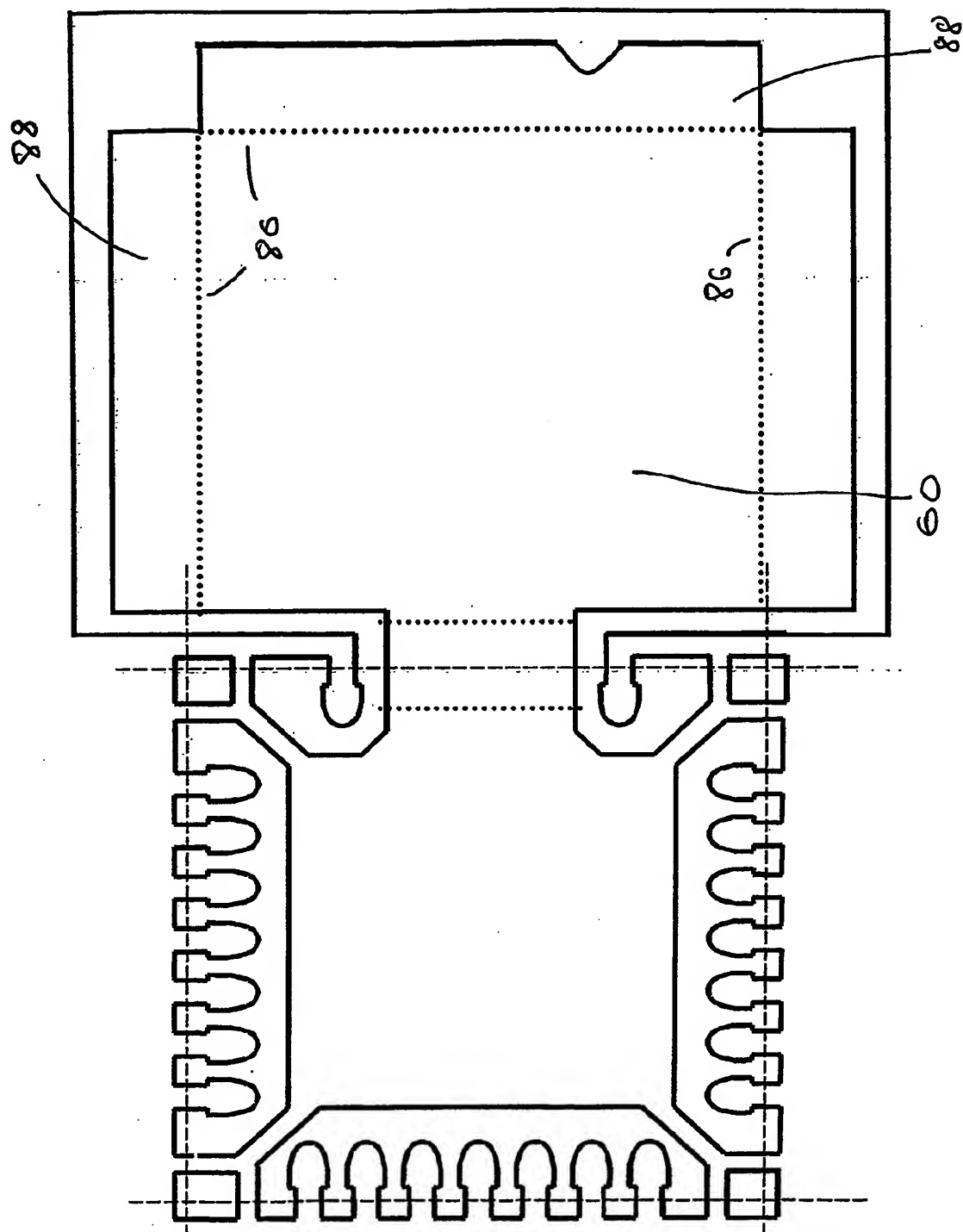


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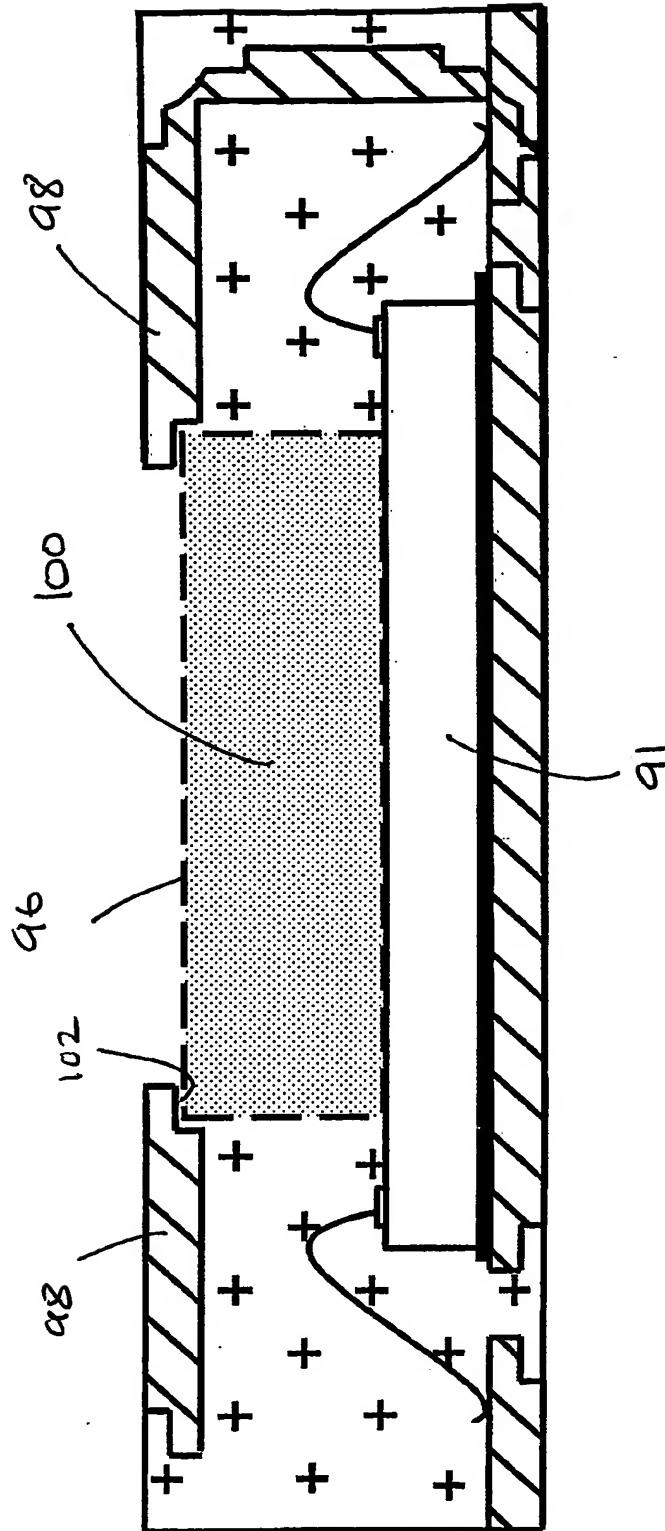


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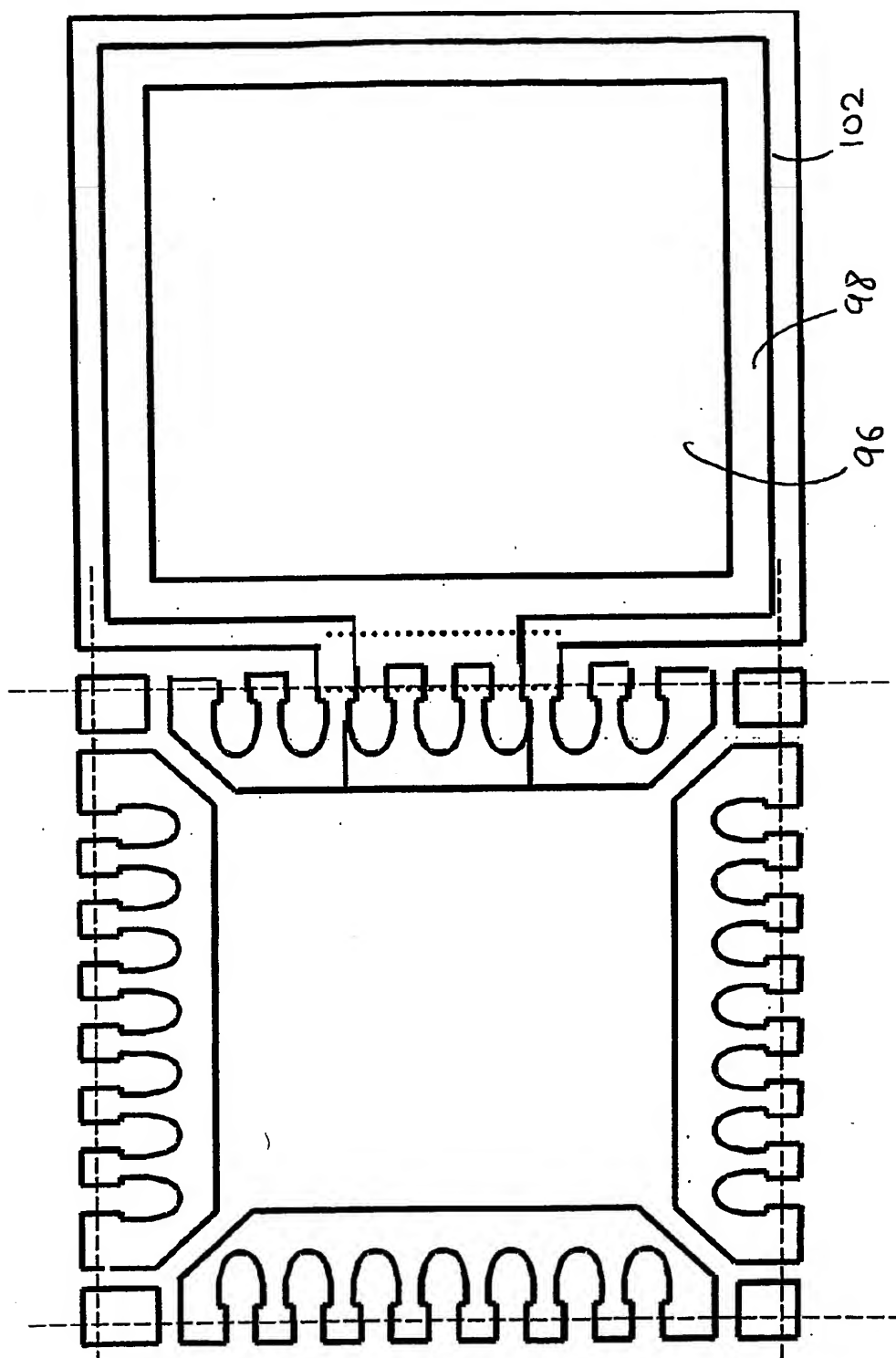


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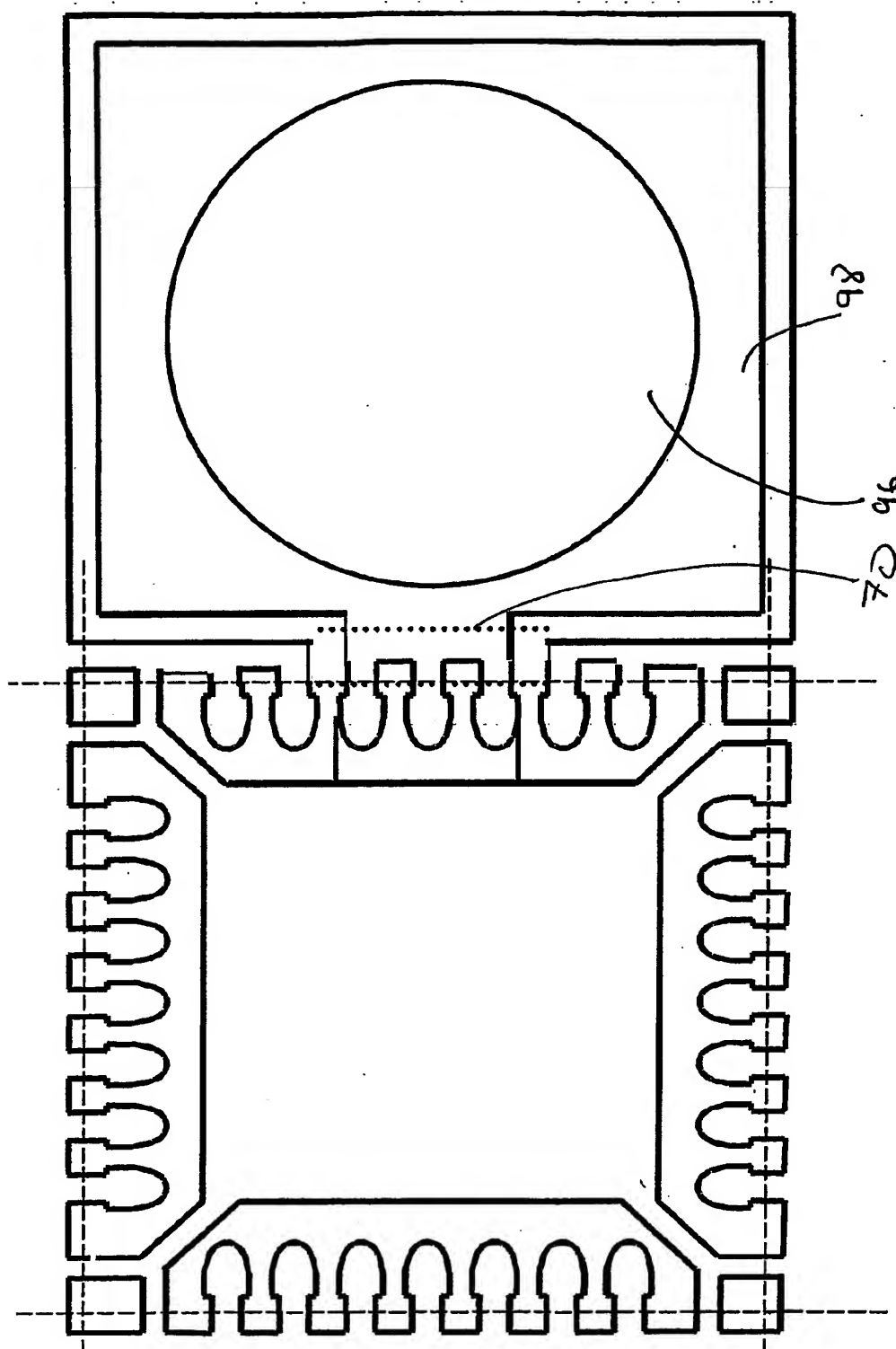


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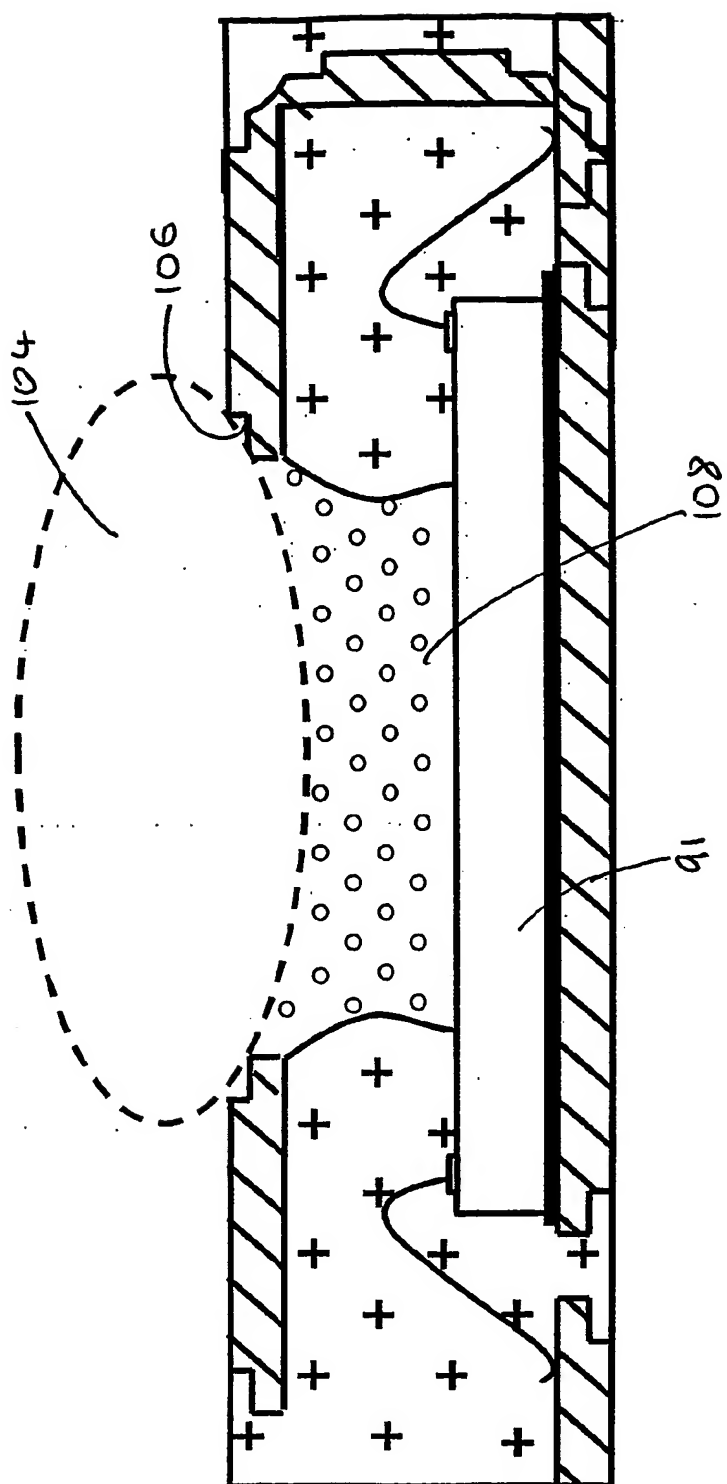


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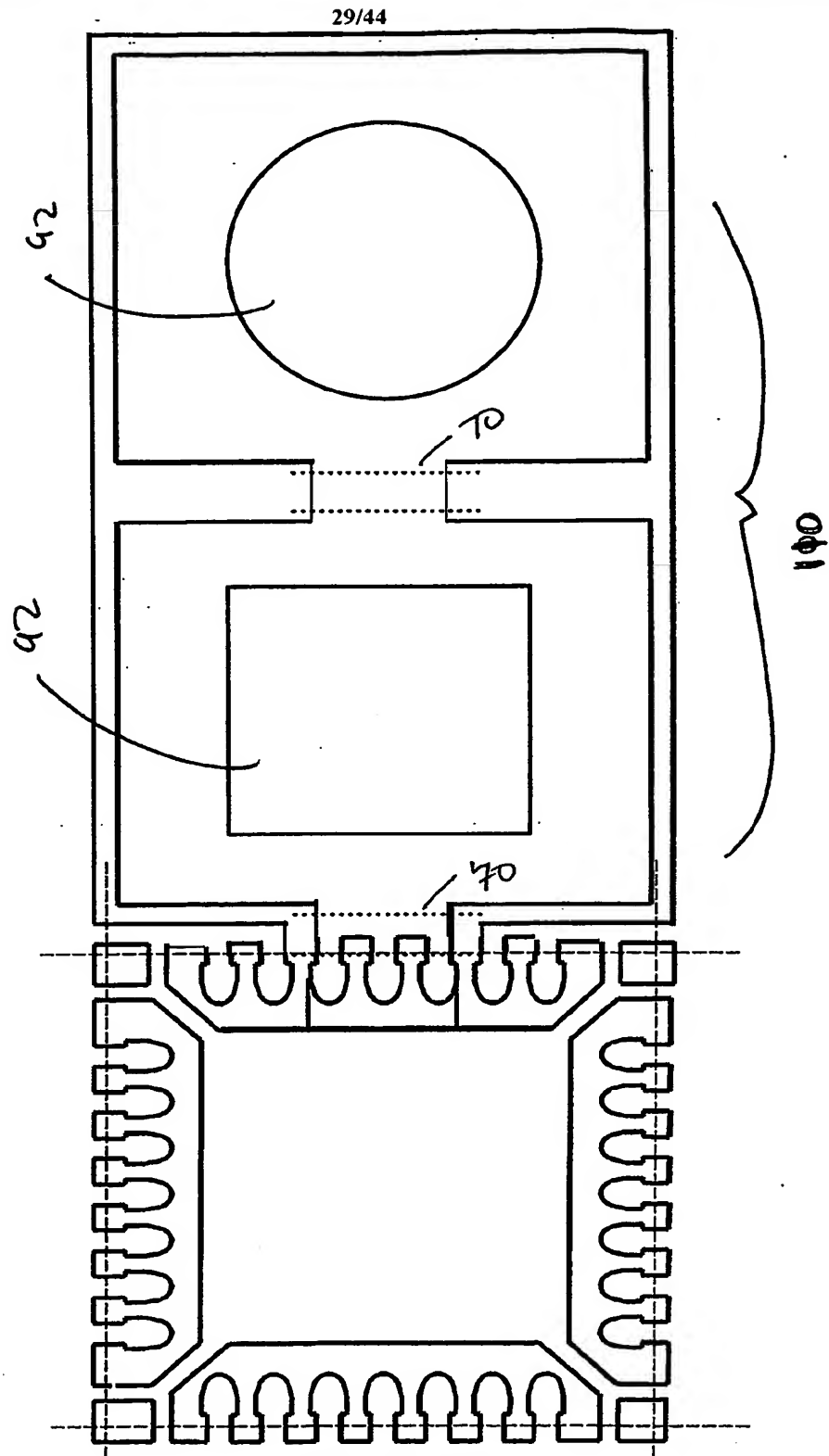


Figure 31

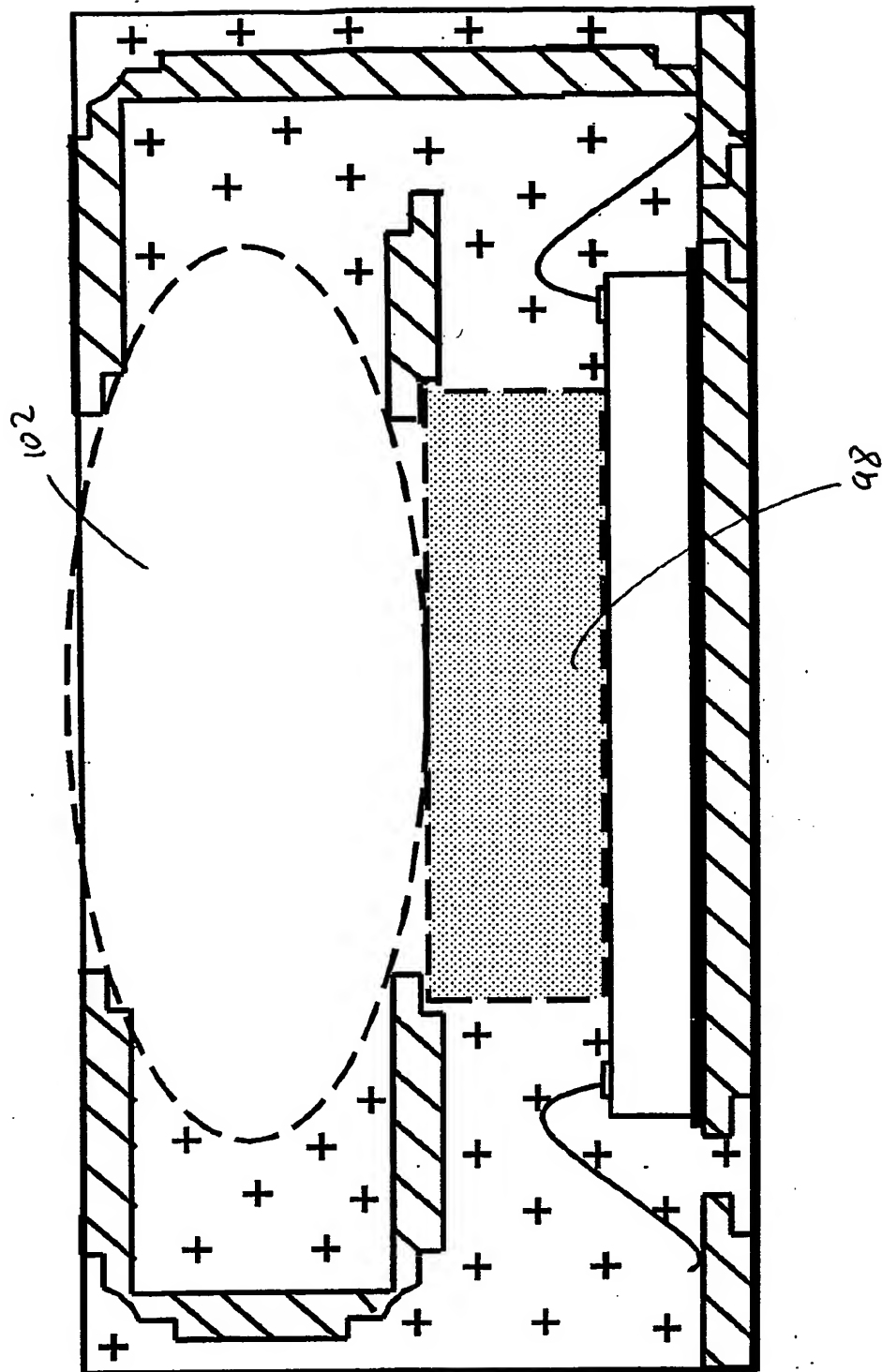


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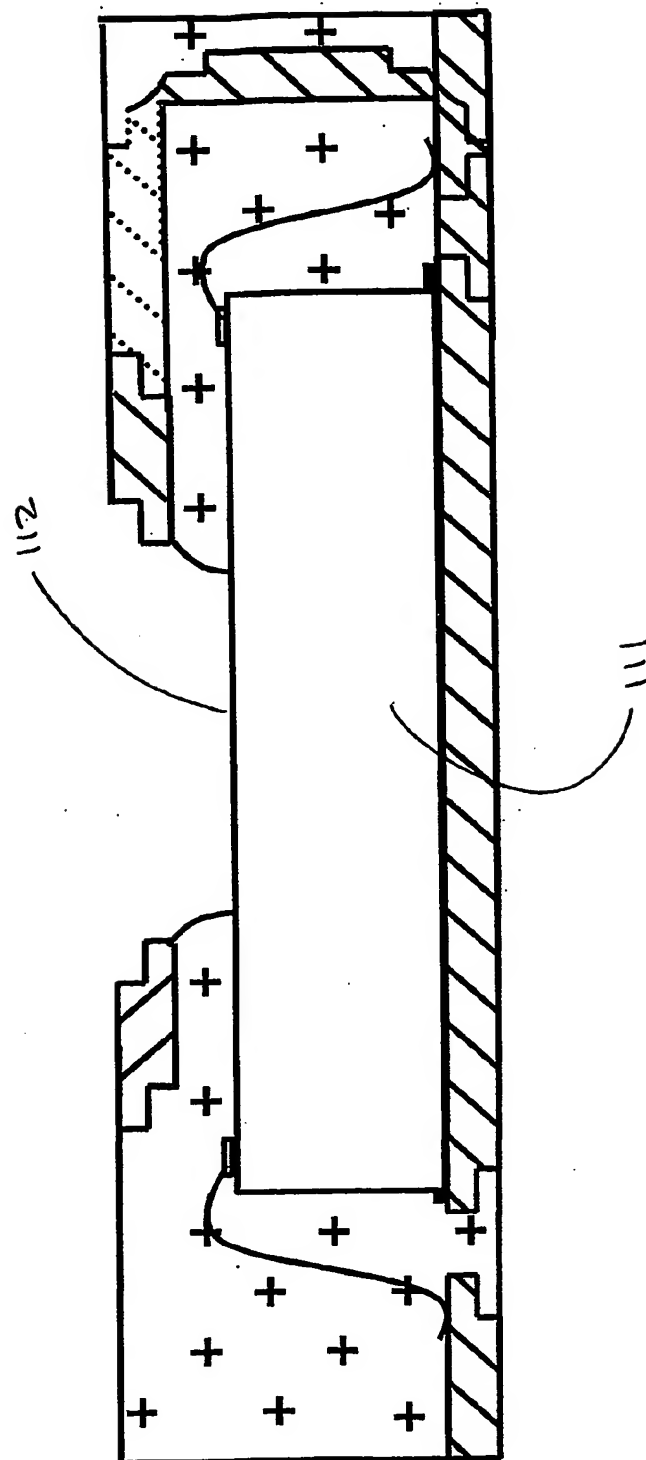


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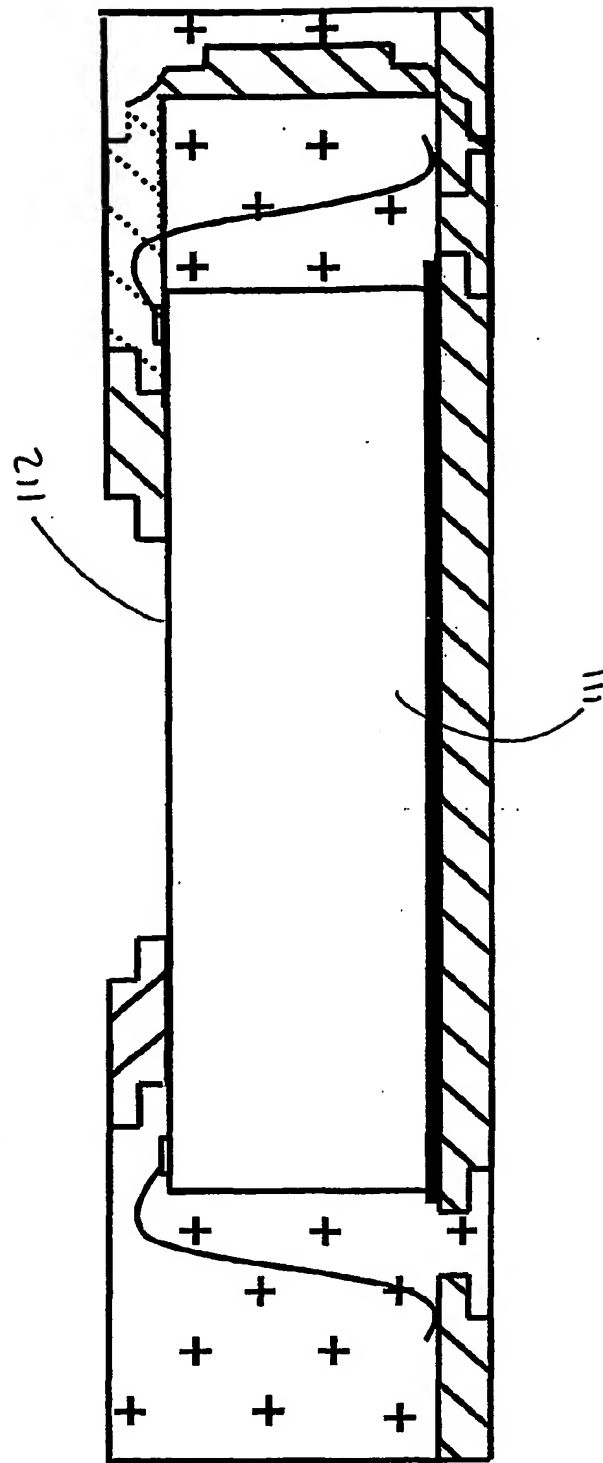


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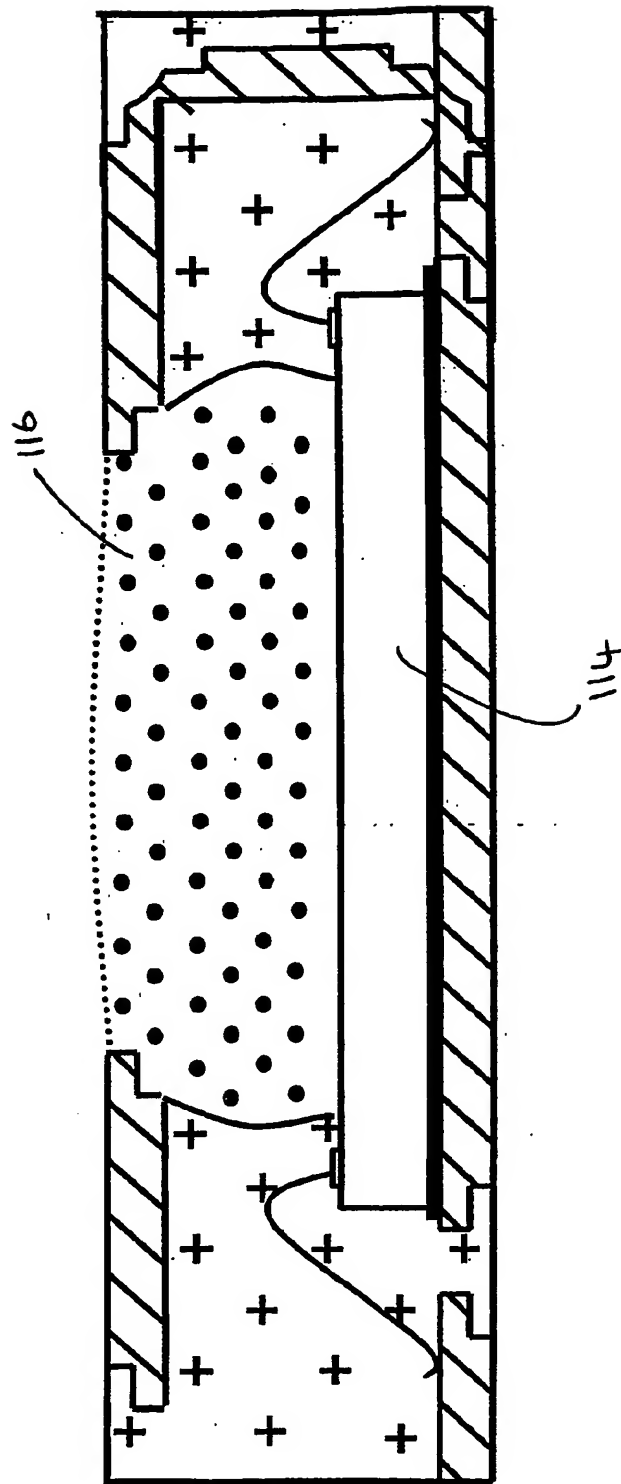


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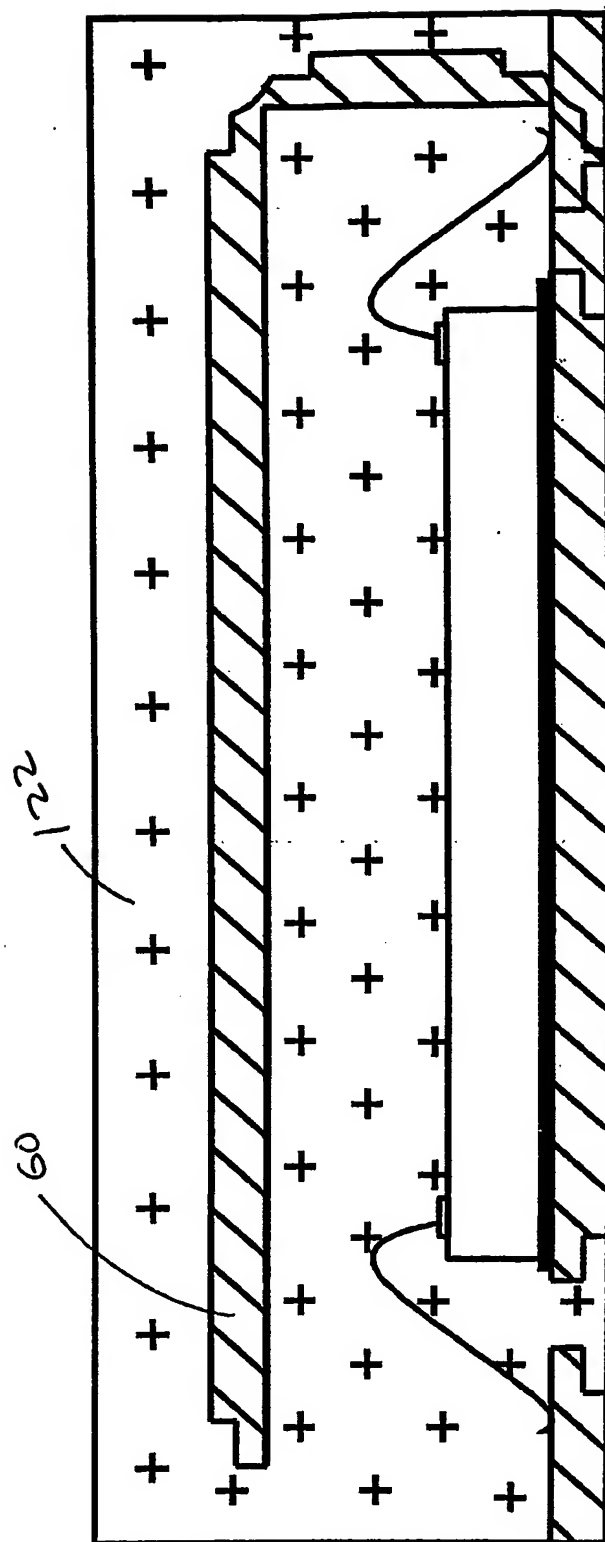


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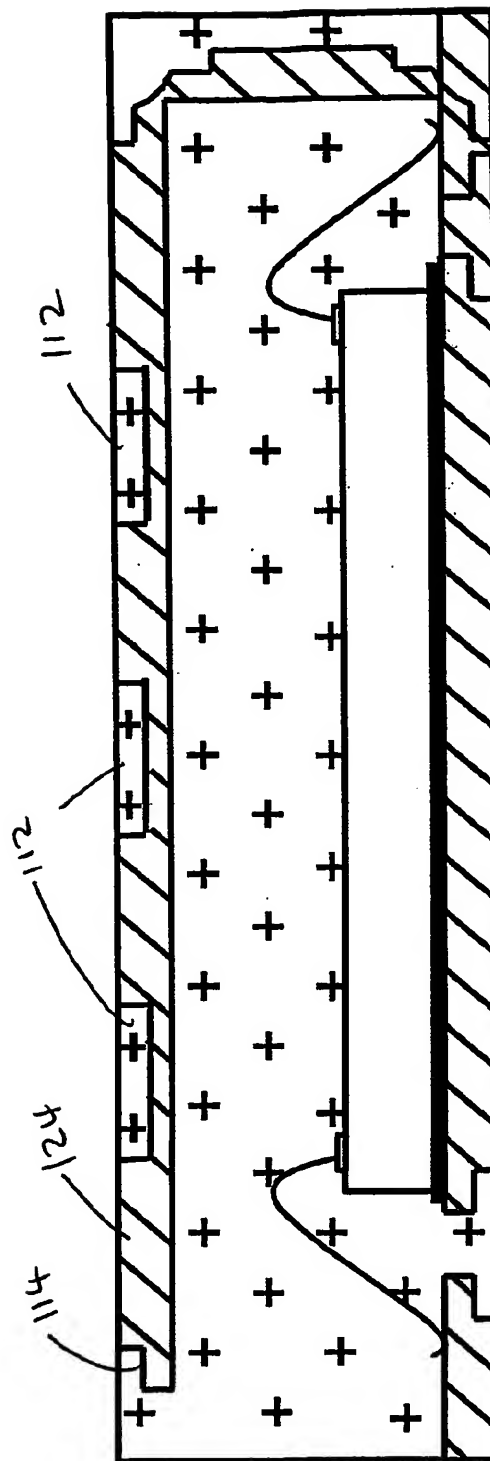


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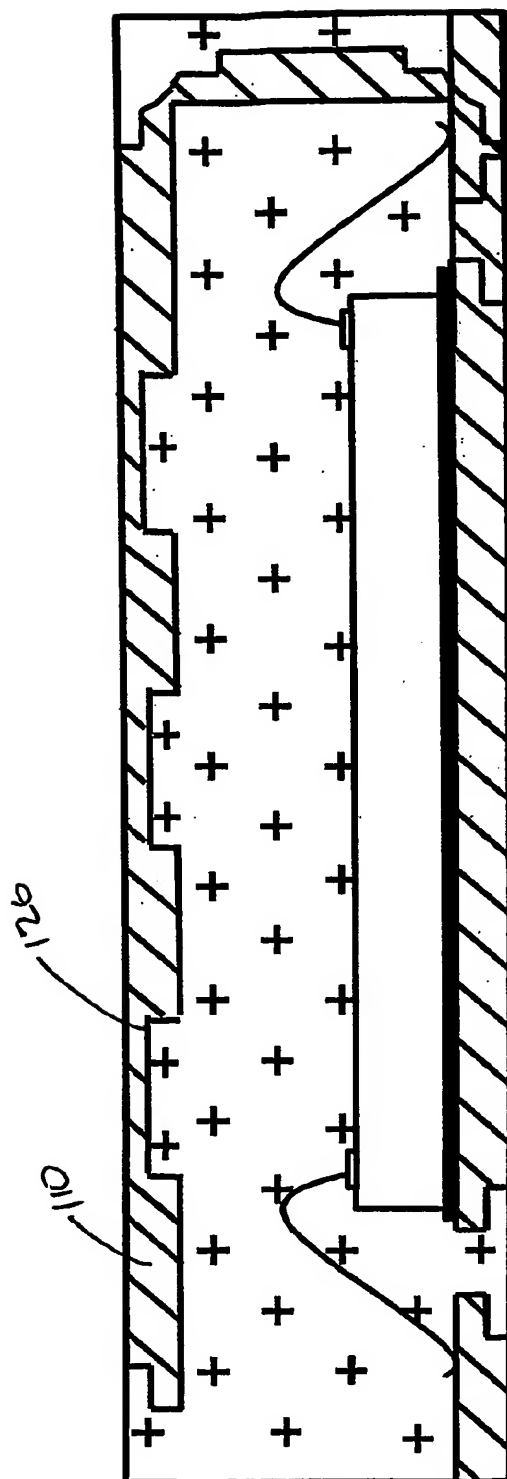


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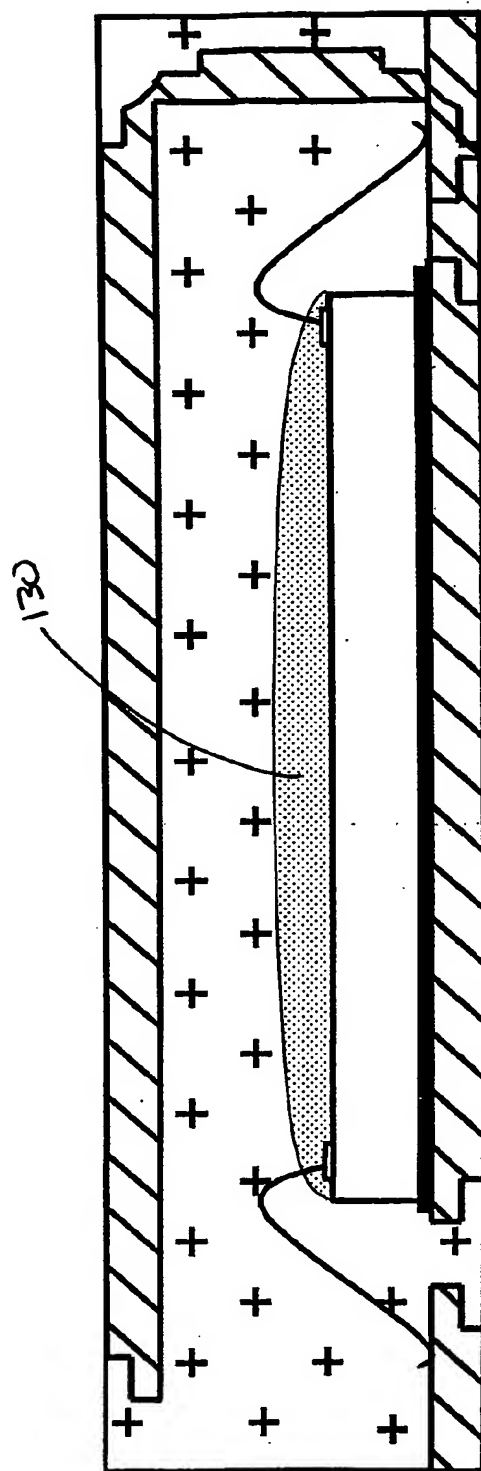


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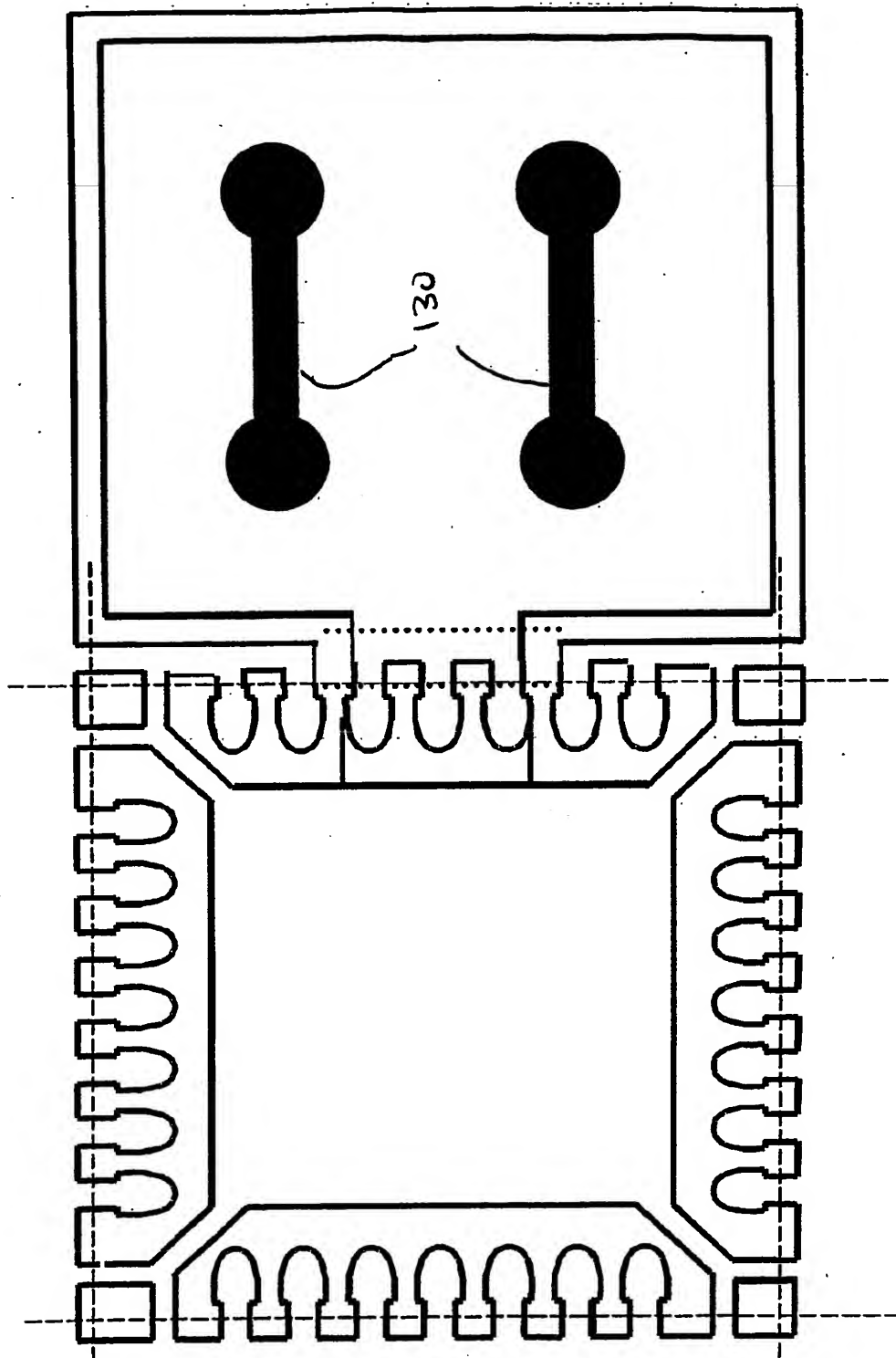


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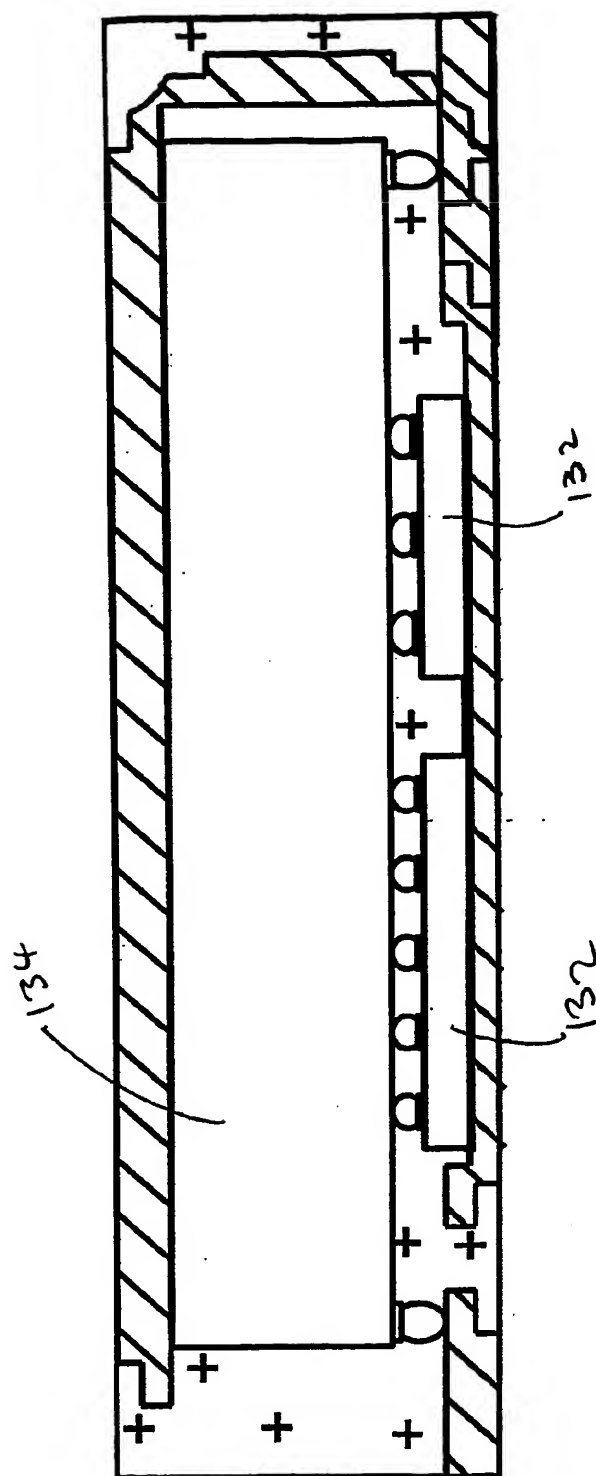


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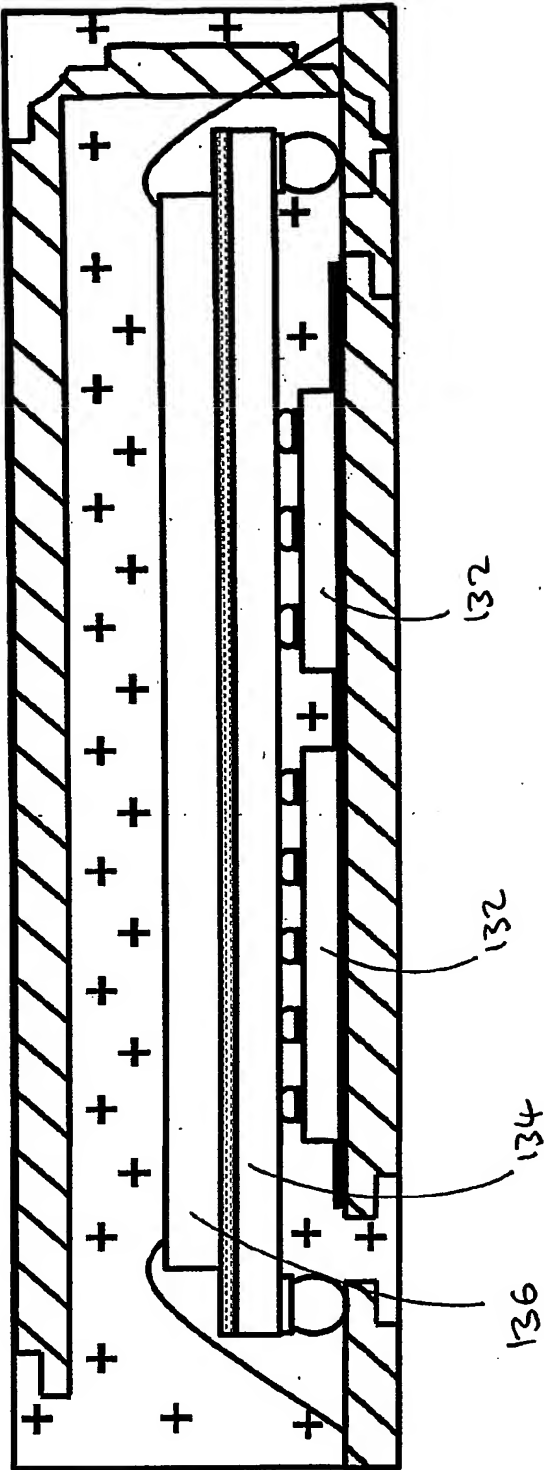


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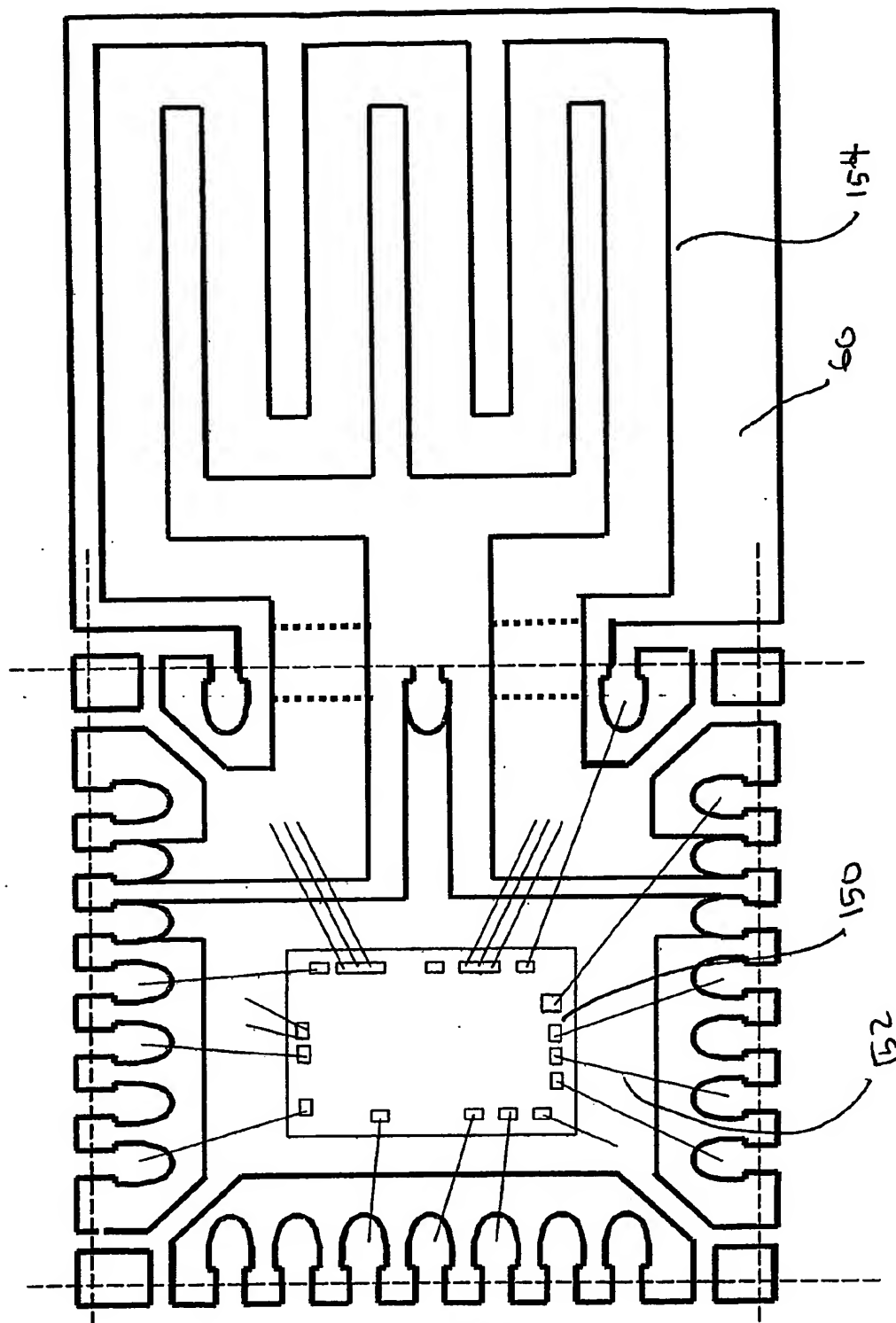


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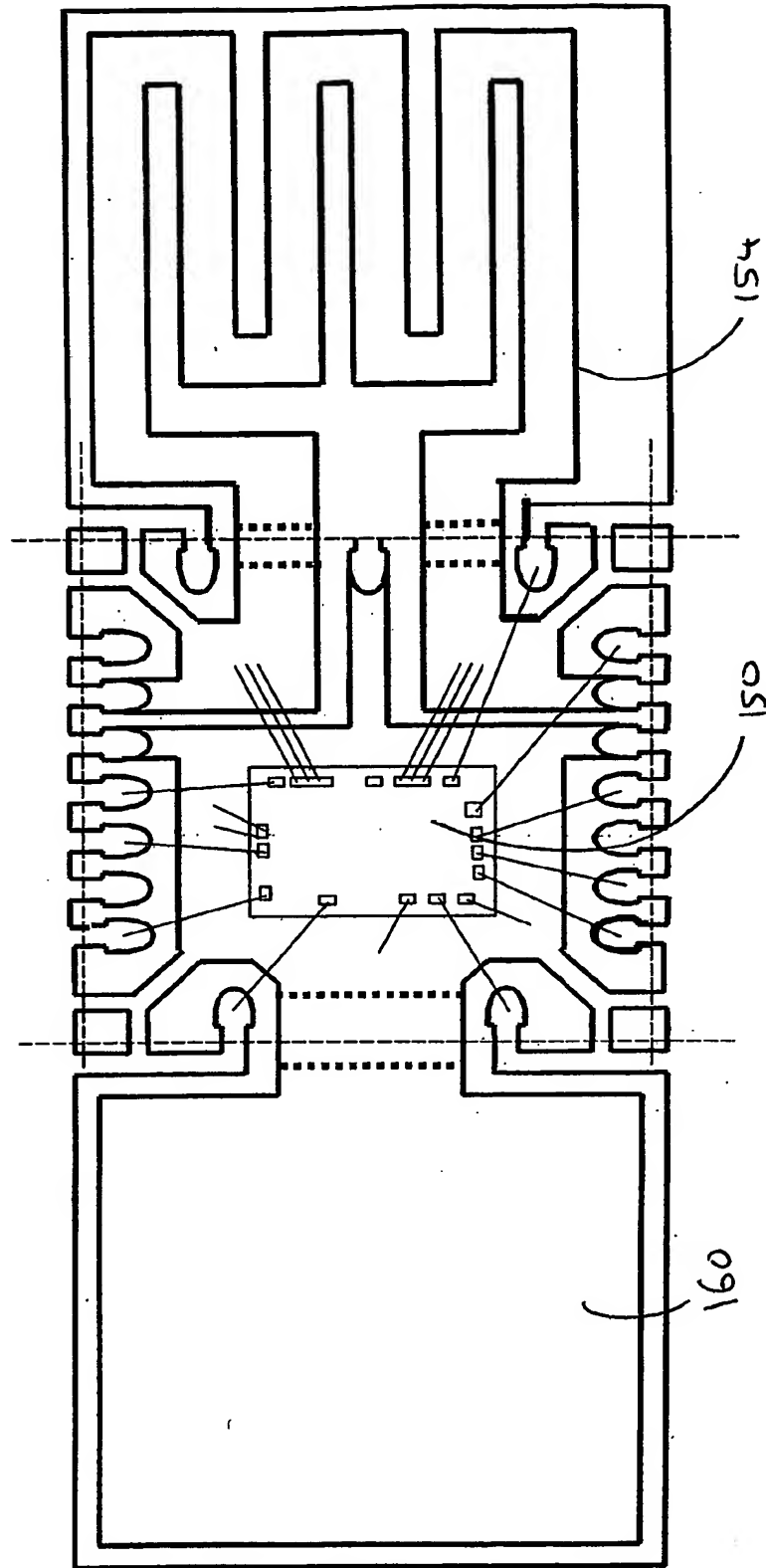


Figure 45

Monitor Point	Frequency	Std Pkg.		New Pkg.		Shield Effectiveness	
		E	H	E	H	E Field	H Field
	GHz	dBV/m	dB μ /m	dBV/m	dB μ /m	dB	dB
+Z	0.9	-2	-21	-12	-42	10	21
+Z	2.4	7	-22	-4	-42	11	20
+Z	5.2	13	-22	5	-41	8	19
+Z	10.0	16	-19	11	-39	5	20

Fig. 46

Semiconductor Chip	Die Size	Material	Power Dissipation
Daughter Die 1	1.8x0.9x0.2mm	Silicon	100mW
Daughter Die 2	2.1x1.1x0.2mm	Gallium Arsenide	1W
Mother Die 3	2.65x2.65x0.2mm	Glass-Quartz	100mW

Fig. 47

Monitor Point	Standard Package	New Package
	Temp (deg C)	Temp (deg C)
Daughter Die 2	137	116
% Improvement	-	22

Fig. 48